

Silicon Tracking Detectors

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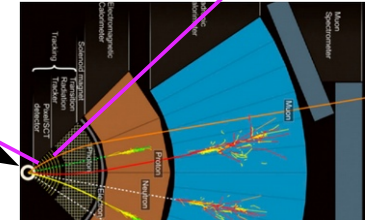
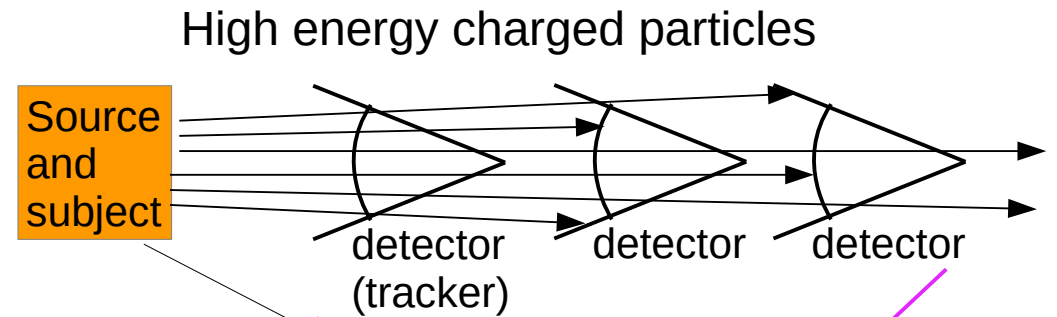
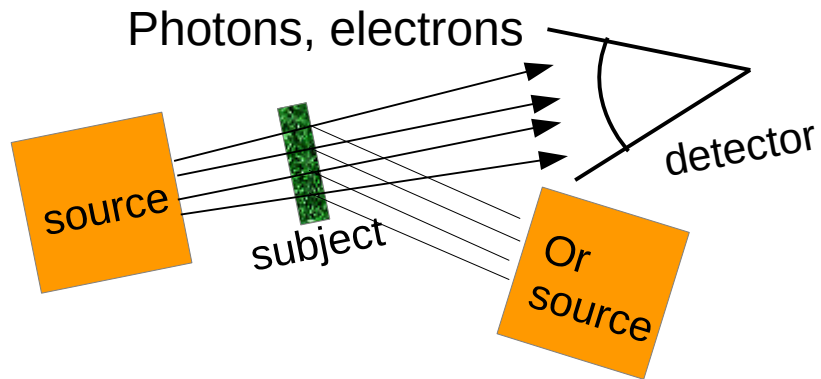
2023 HEPIC Summer Week – SLAC

Close-up of ATLAS pixel detector, installed in 2007

M/S Pledge

I pledge to not use the words Master and Slave to designate components or roles in circuits, systems,

<https://sites.google.com/view/mspledge/>

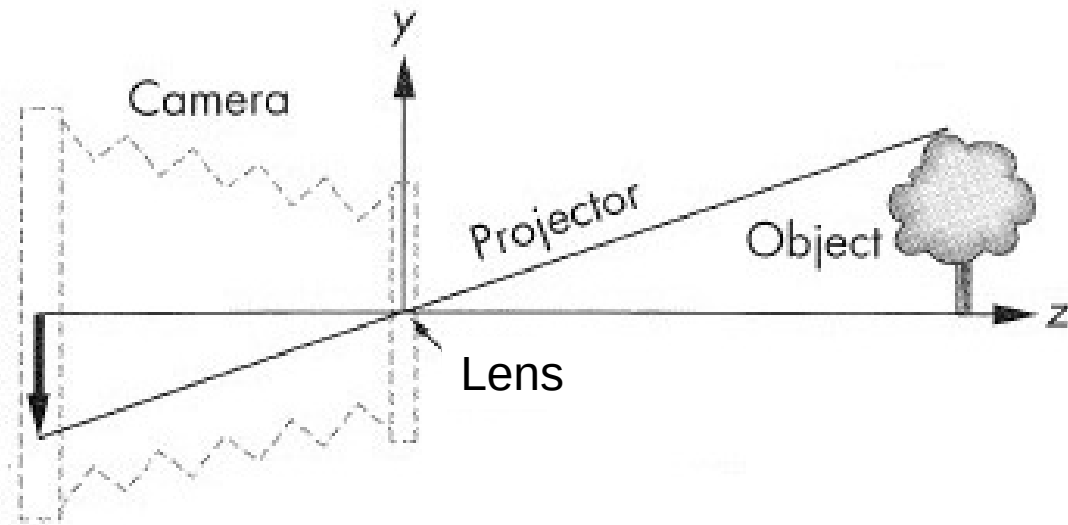


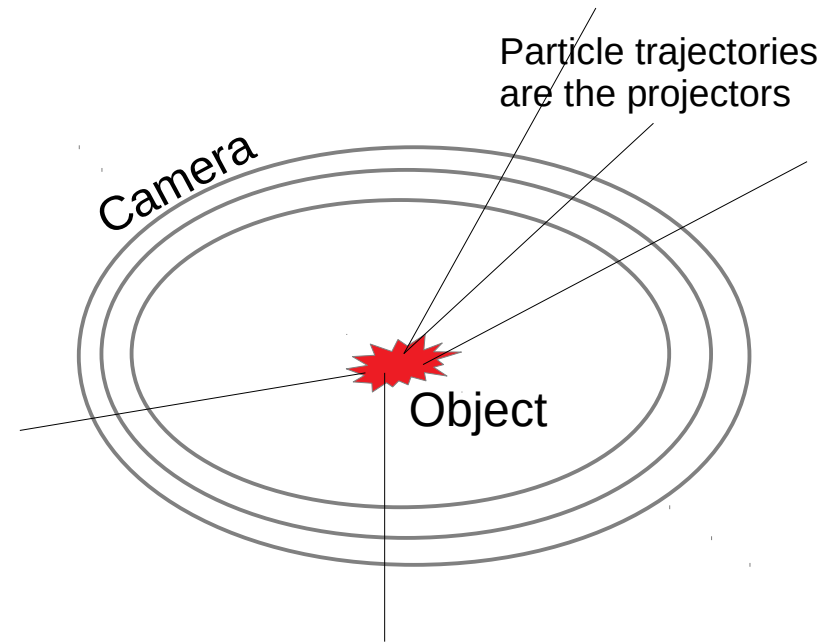
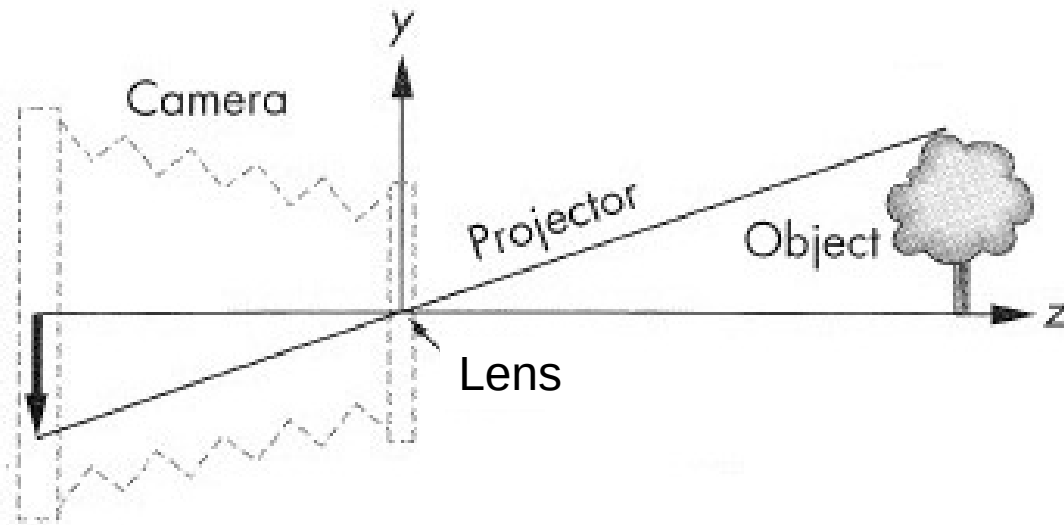
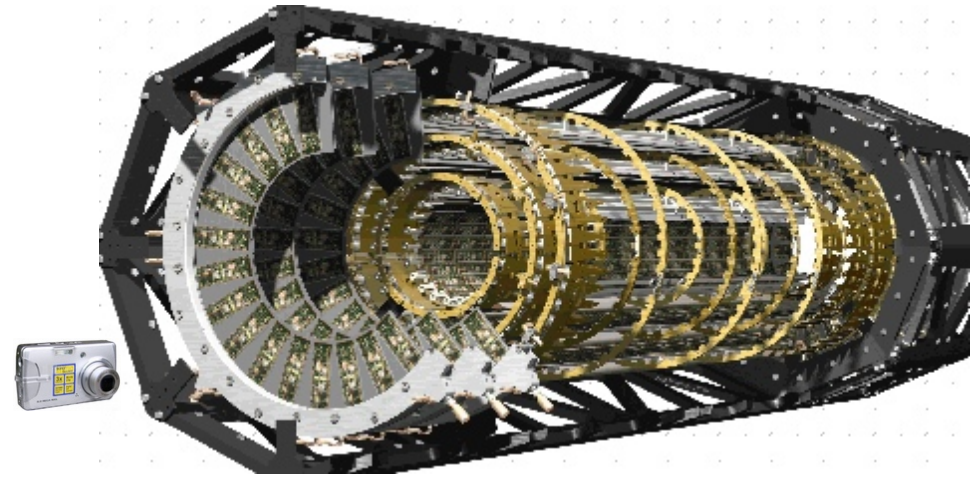
- **What you're used to:**

- **Detector to completely stops photons**
- **Lots of photons- every pixel gets some- source intensity limited on purpose**
- **Integrate or count many photons per channel**

- **Crucial differences for Imaging high energy charged particles**

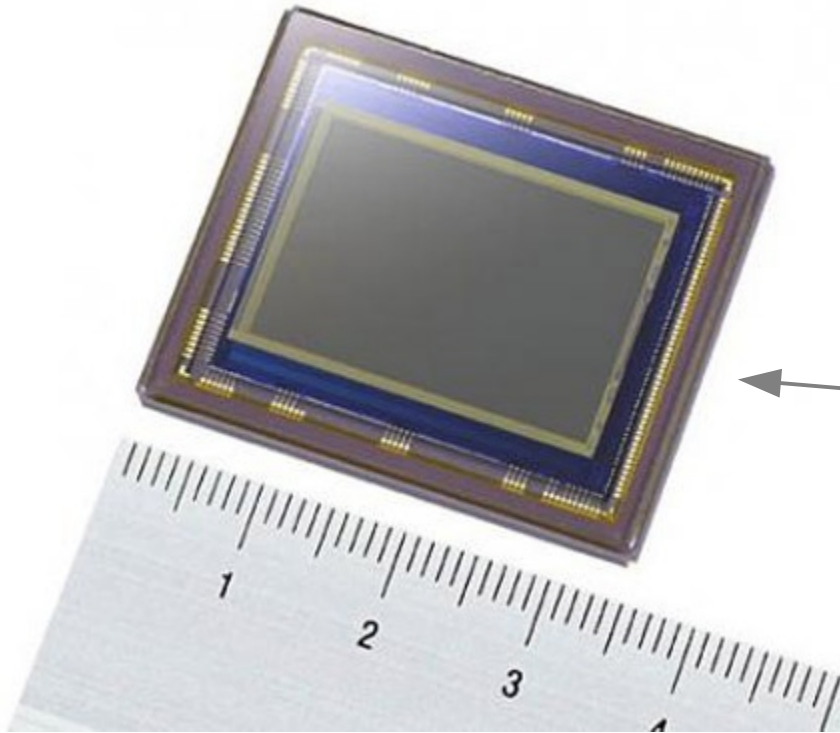
- **Want particles to pass thorough imaging detector (aka tracker) as if it was not there. There are other detectors behind it**
- **There is no sample. We are looking at the quantum vacuum. Want intensity as high as possible.**
- **Measure every particle individually**





Clear?

Let's build ourselves a silicon pixel tracking detector



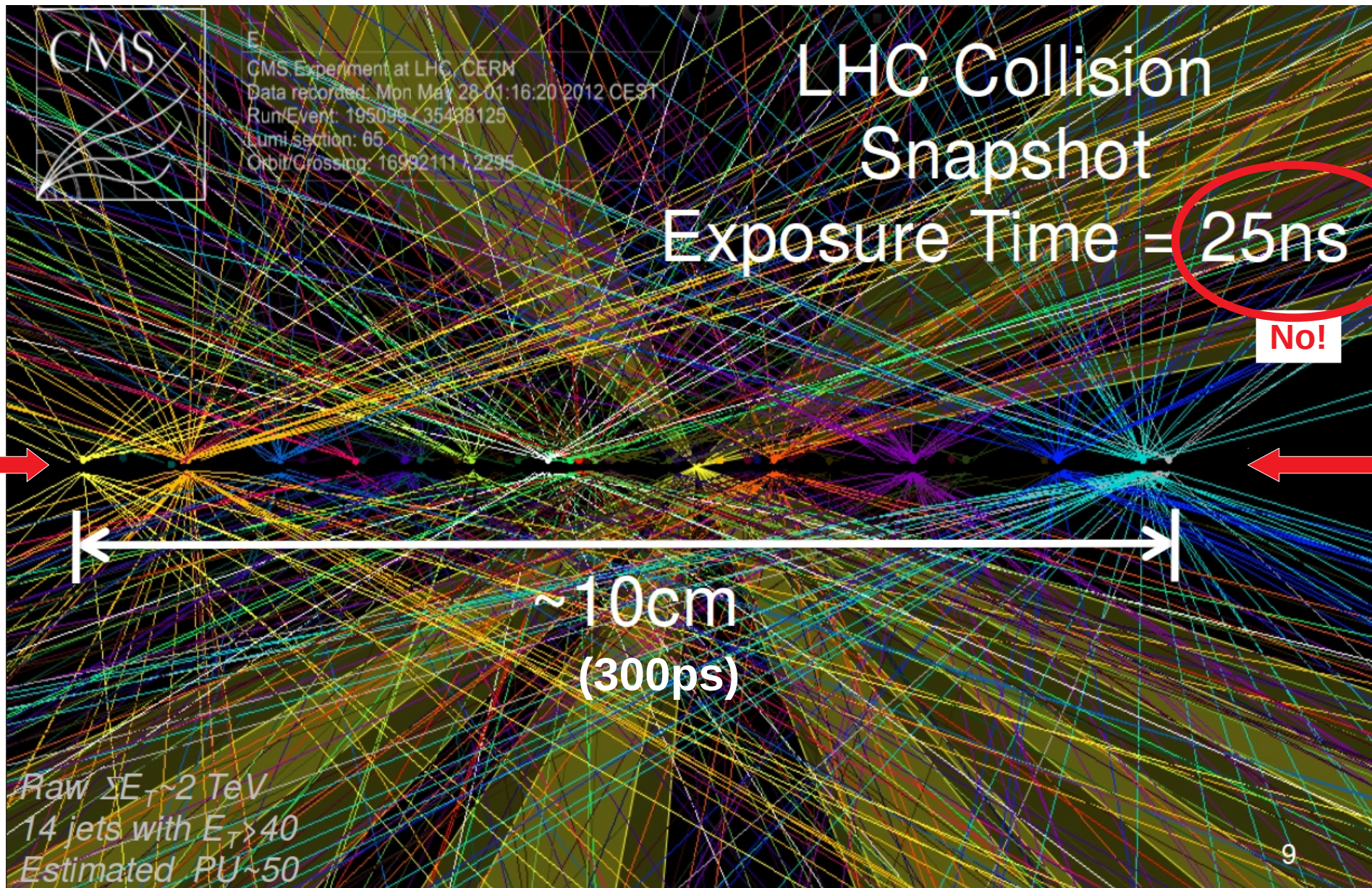
$\sim 2 \text{ cm}^2$

Surround interaction point with few layers of sensors

$\sim 100\,000 \text{ cm}^2$

(\$500K plus tax)

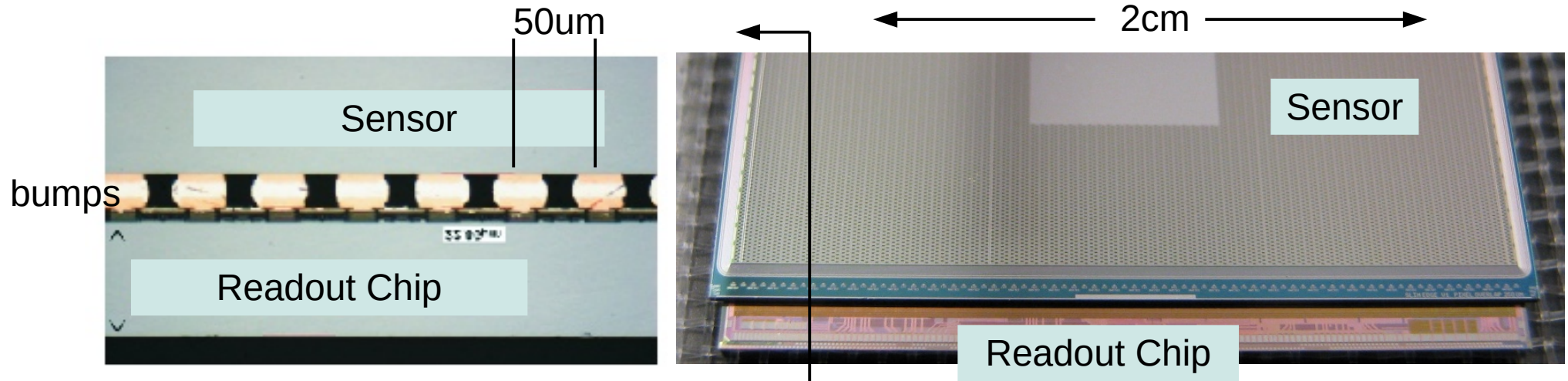




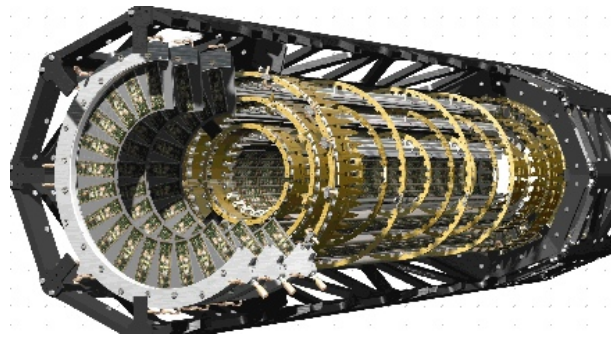
- OK, so this thing can do 30 fps right?



- Then instead of 50,000 sensors we need $(40,000,000 / 30) * 50,000 = 65B$ sensors, which will only cost us \$650B. Maybe we can get a volume discount?
-
-
-
- And that's why we need custom ASICs to make tracking detectors
- Review how they're actually made next (or just remember the tour)



ATLAS
PIXEL
2007
80M pixels

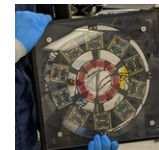


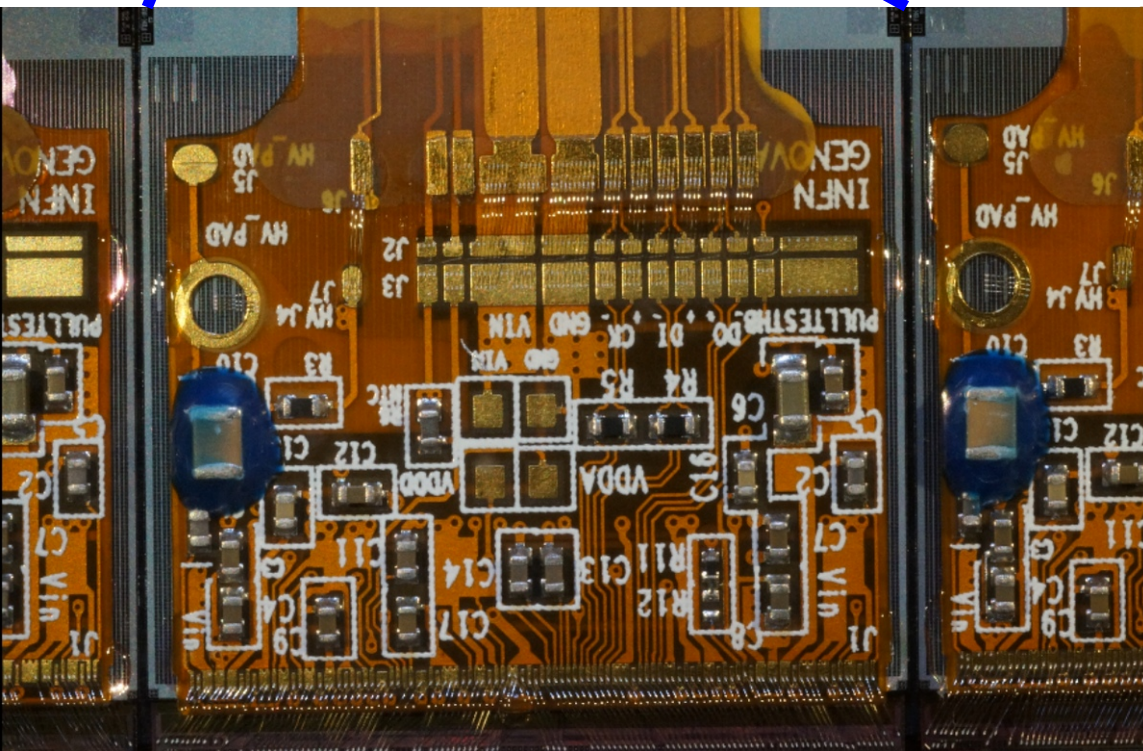
ATLAS
IBL
2014
12M pixels



ATLAS ITK 2026, 5G pixels

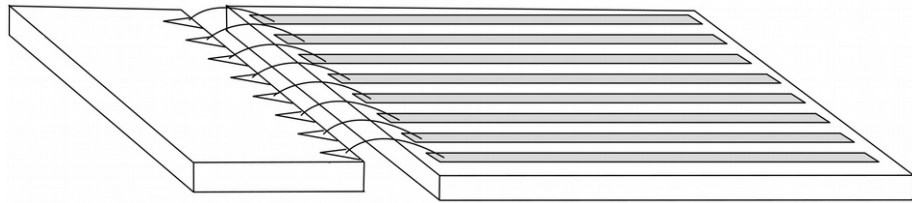
Remember the tour...



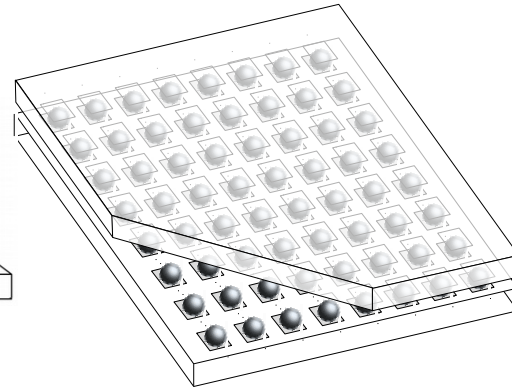


ATLAS beam pipe layer (IBL)

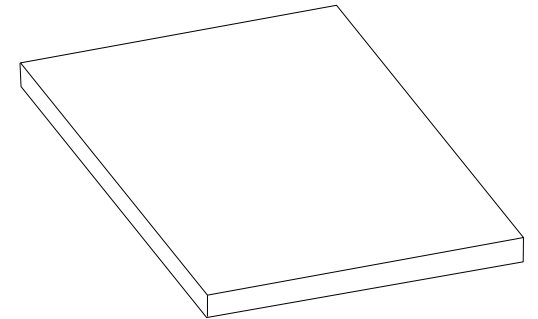
- Radiation dose: 5×10^{15} n_eq/cm²
- “Frame rate”: 40 MHz
- Pixel size: 50 μ m x 250 μ m
- Silicon area: 0.15 m²



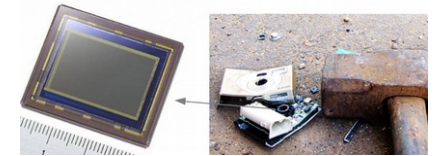
Hybrid Strips

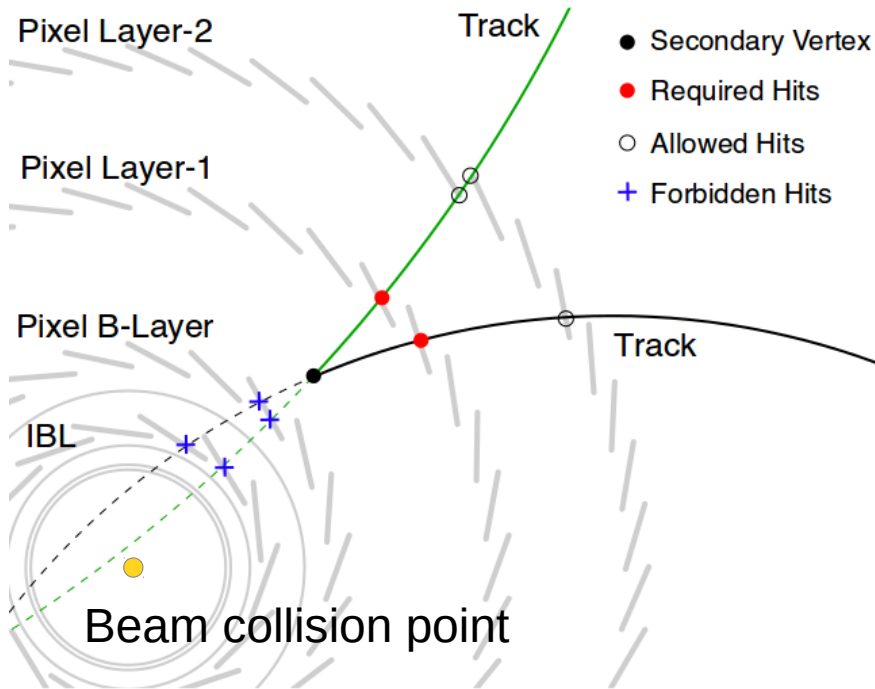


Hybrid Pixels



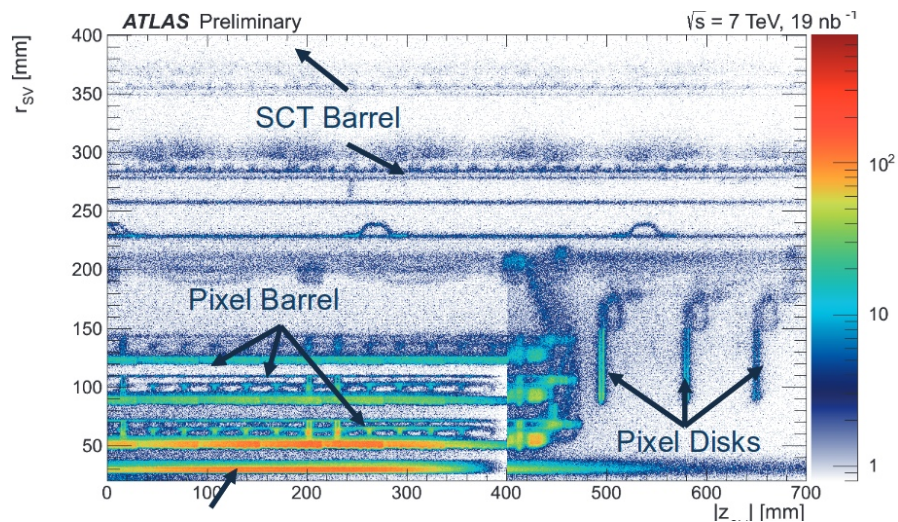
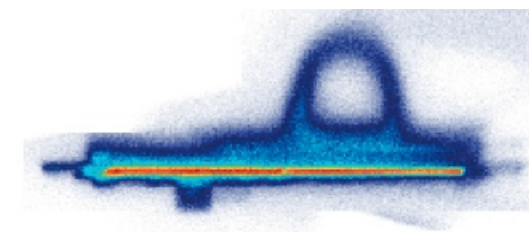
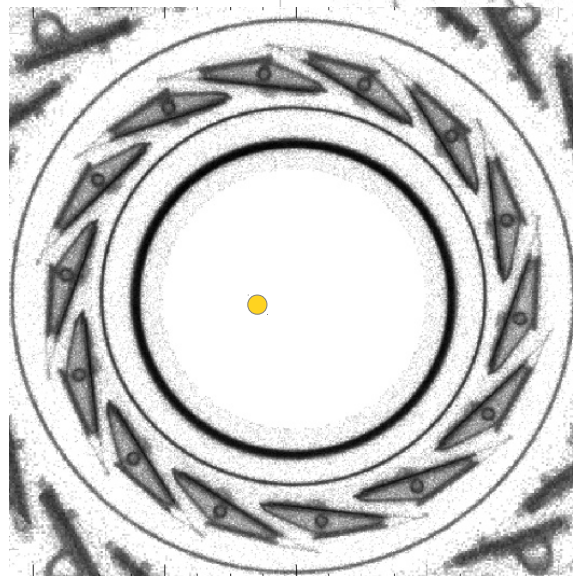
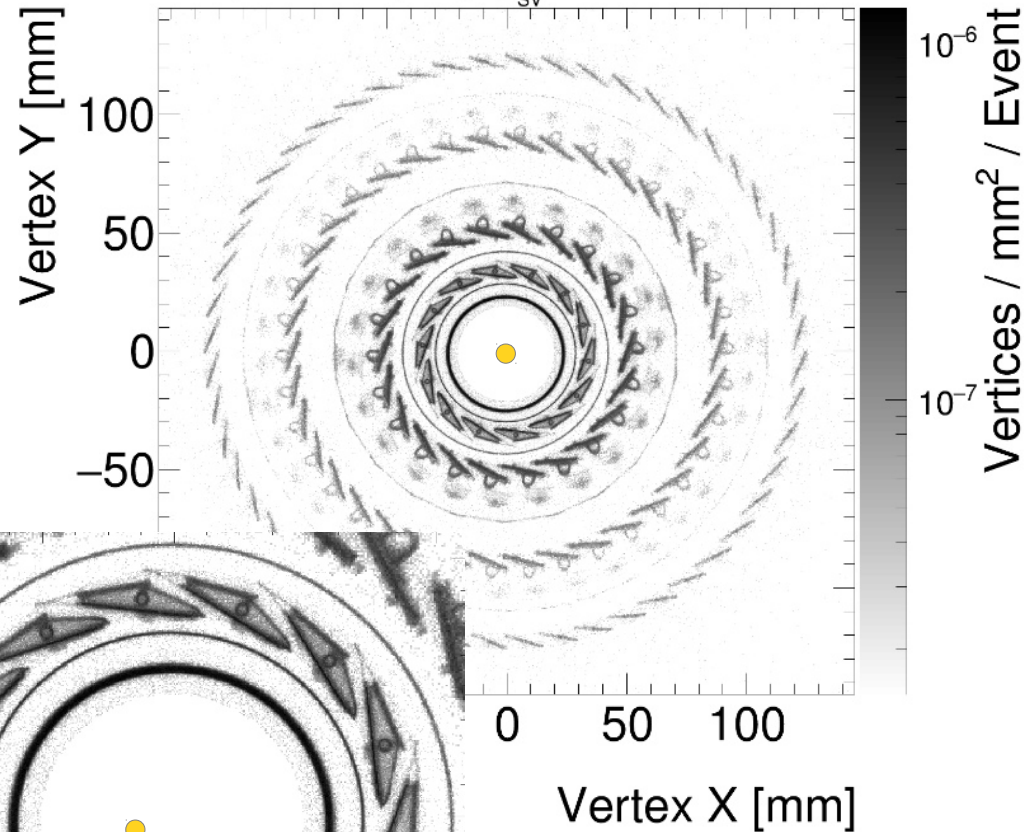
Monolithic

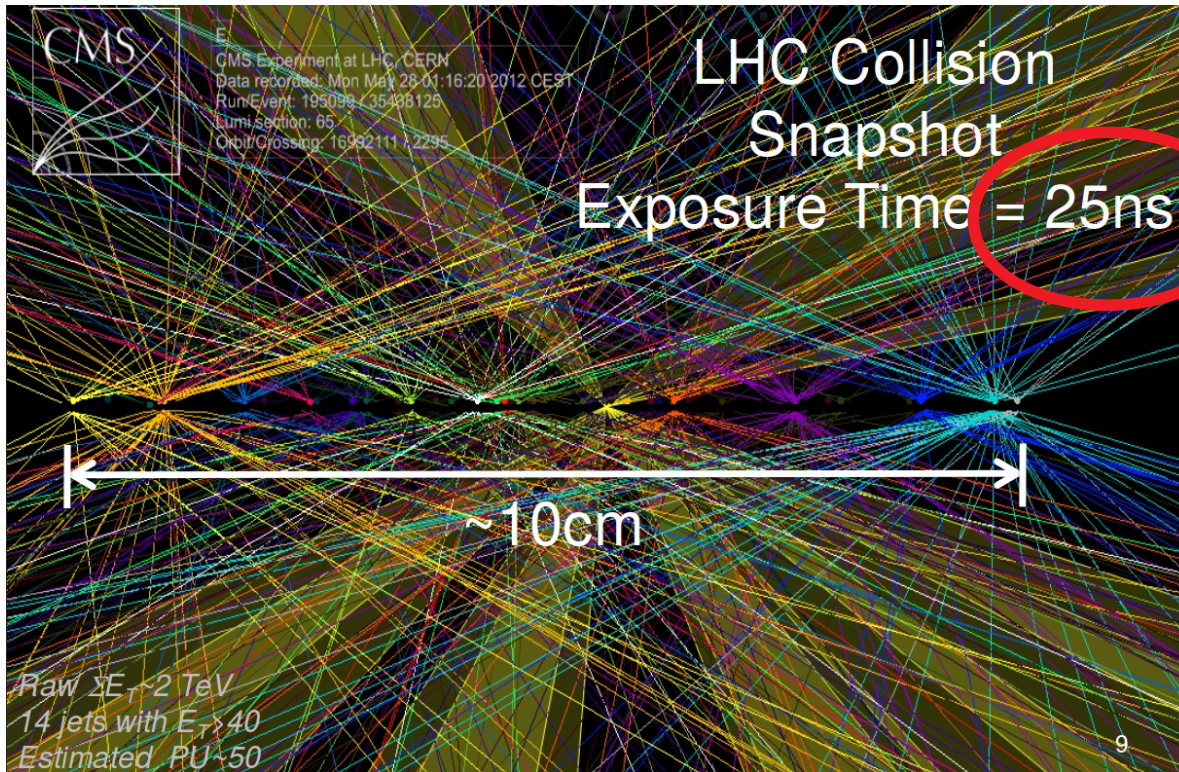




ATLAS Preliminary

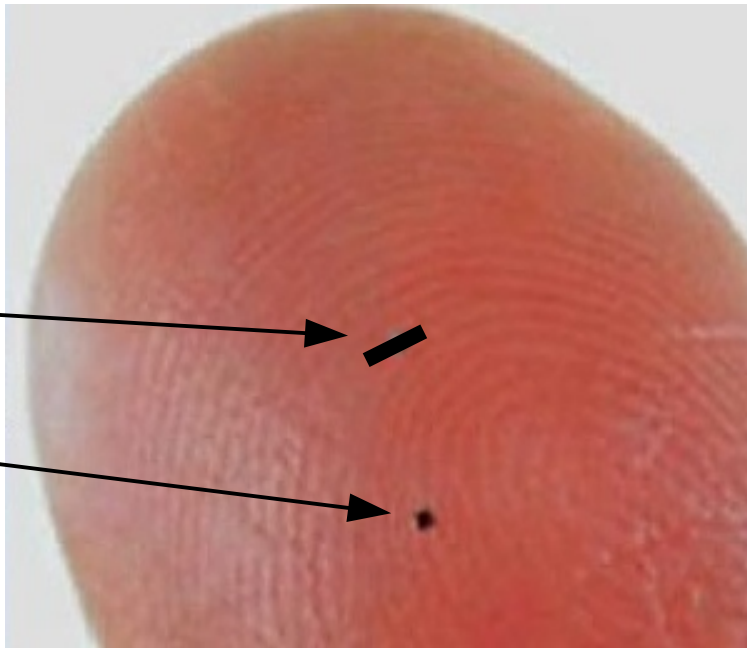
Data $\sqrt{s} = 13$ TeV (2015) $|\eta_{SV}| < 2.4$





- Capturing 40M 5Gpixel images per second is not feasible.
- Triggering only saves a factor of 40 in readout
 - 1M 5Gpixel images per second is still far from feasible
- A: We do NOT do conventional image capture.
- We treat every pixel as an independent, free-running detector and store it's output (heavily redacted)

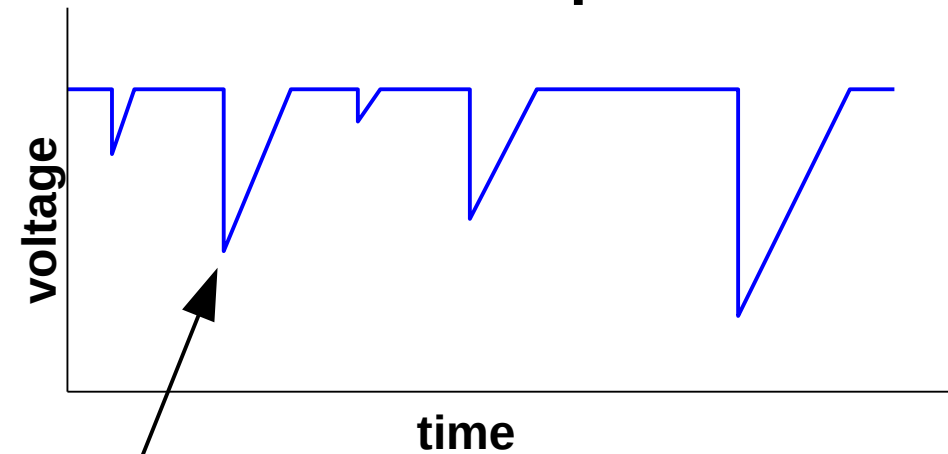
Pixel size



IBL →

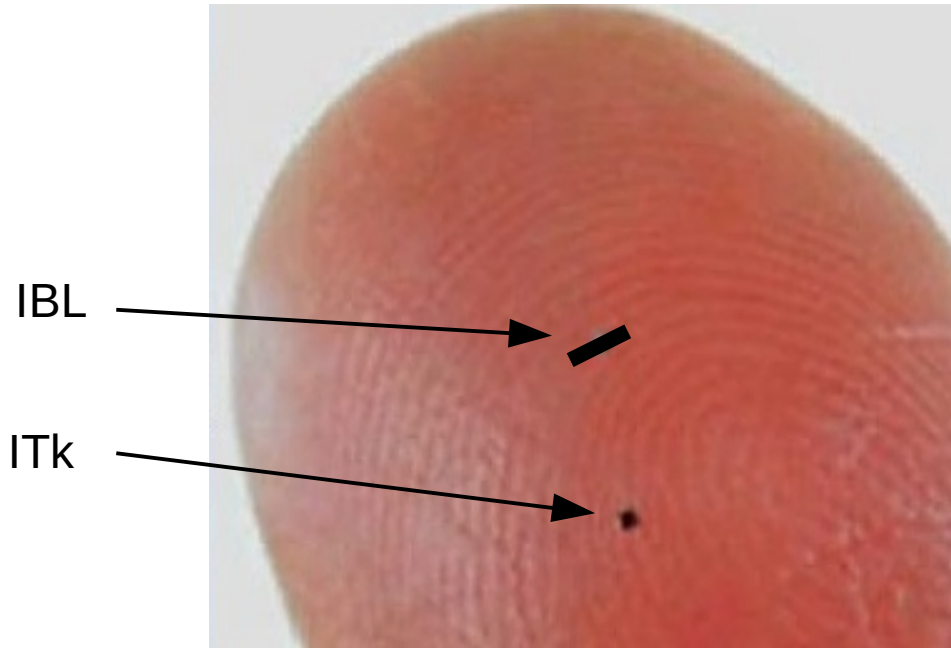
ITk →

Pixel output

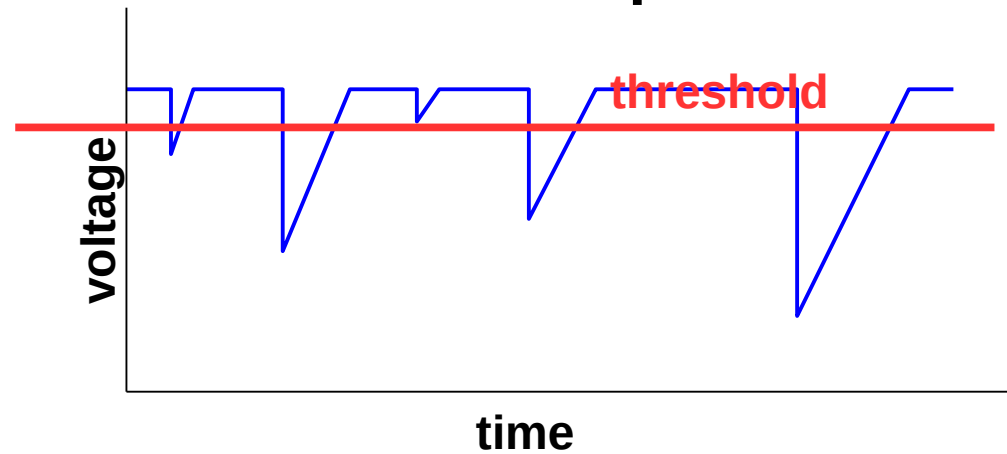


Hits
~50 kHz
(not too bad compared to 40 MHz)

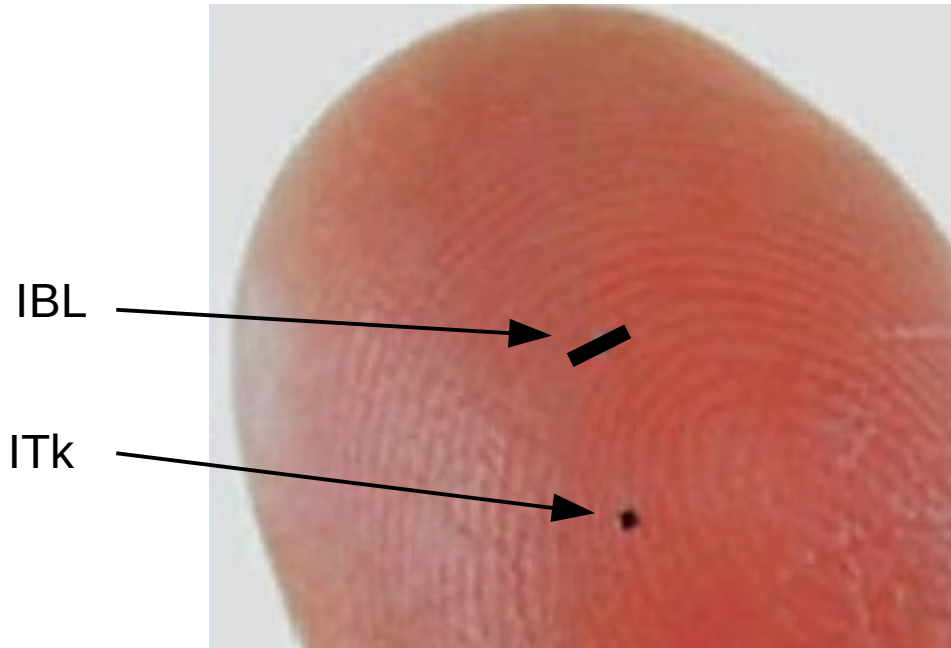
Pixel size



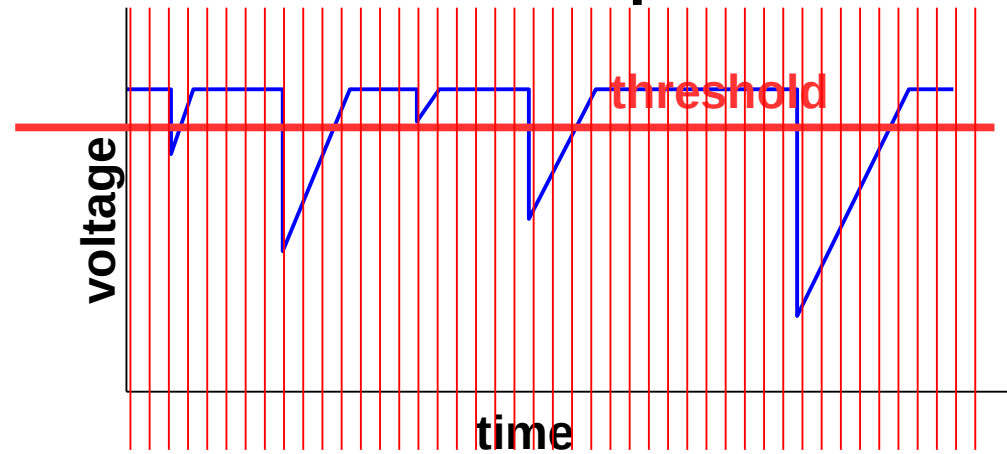
Pixel output



Pixel size

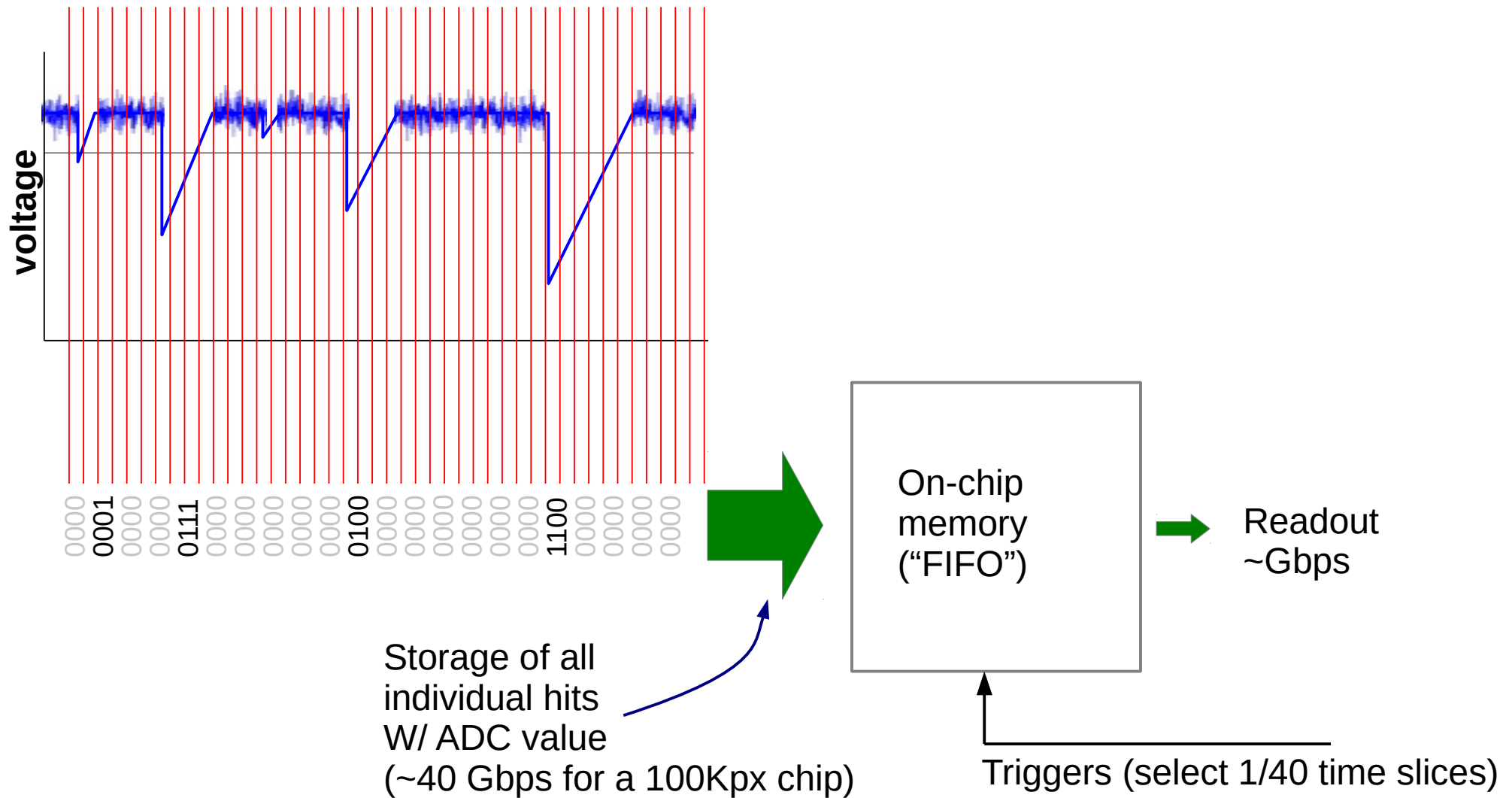


Pixel output

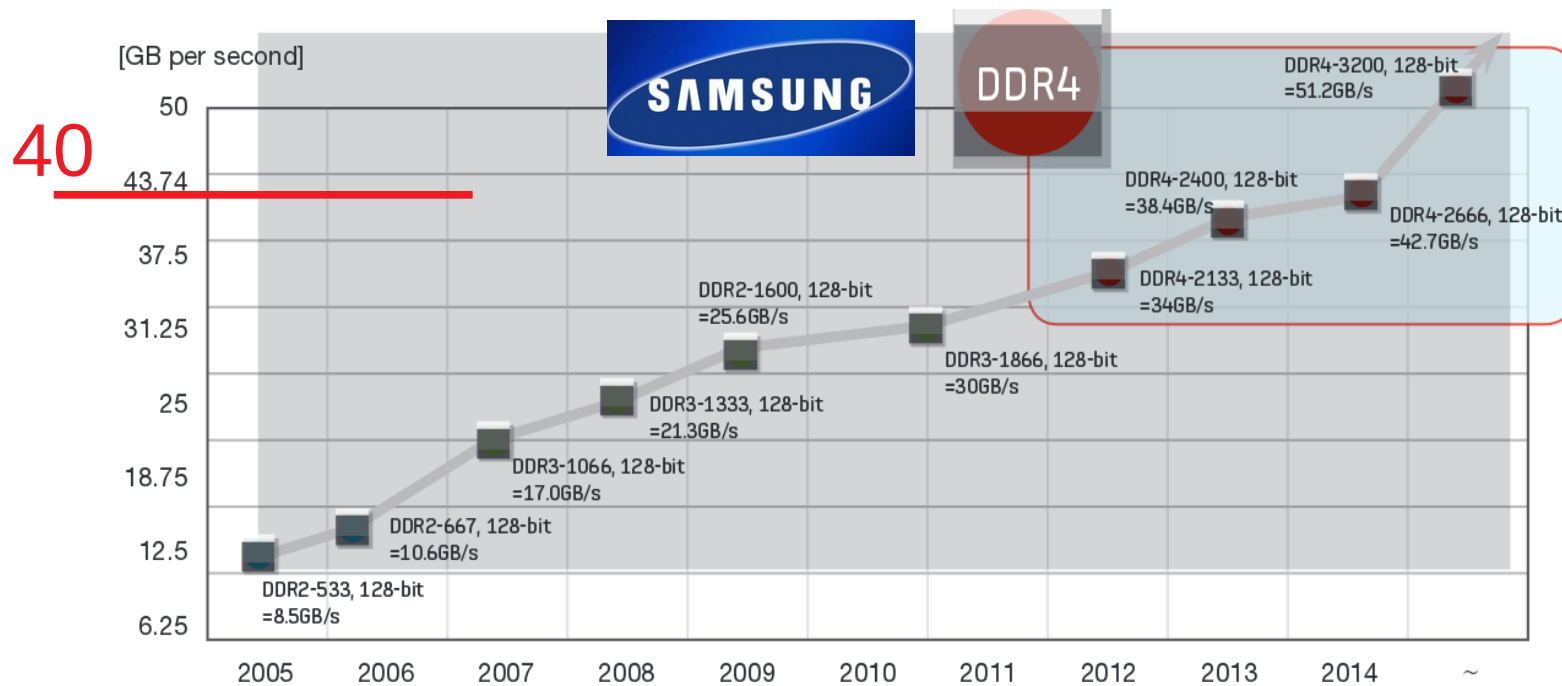


Bunch crossings

Digitize amplitude above threshold in each Bunch Crossing



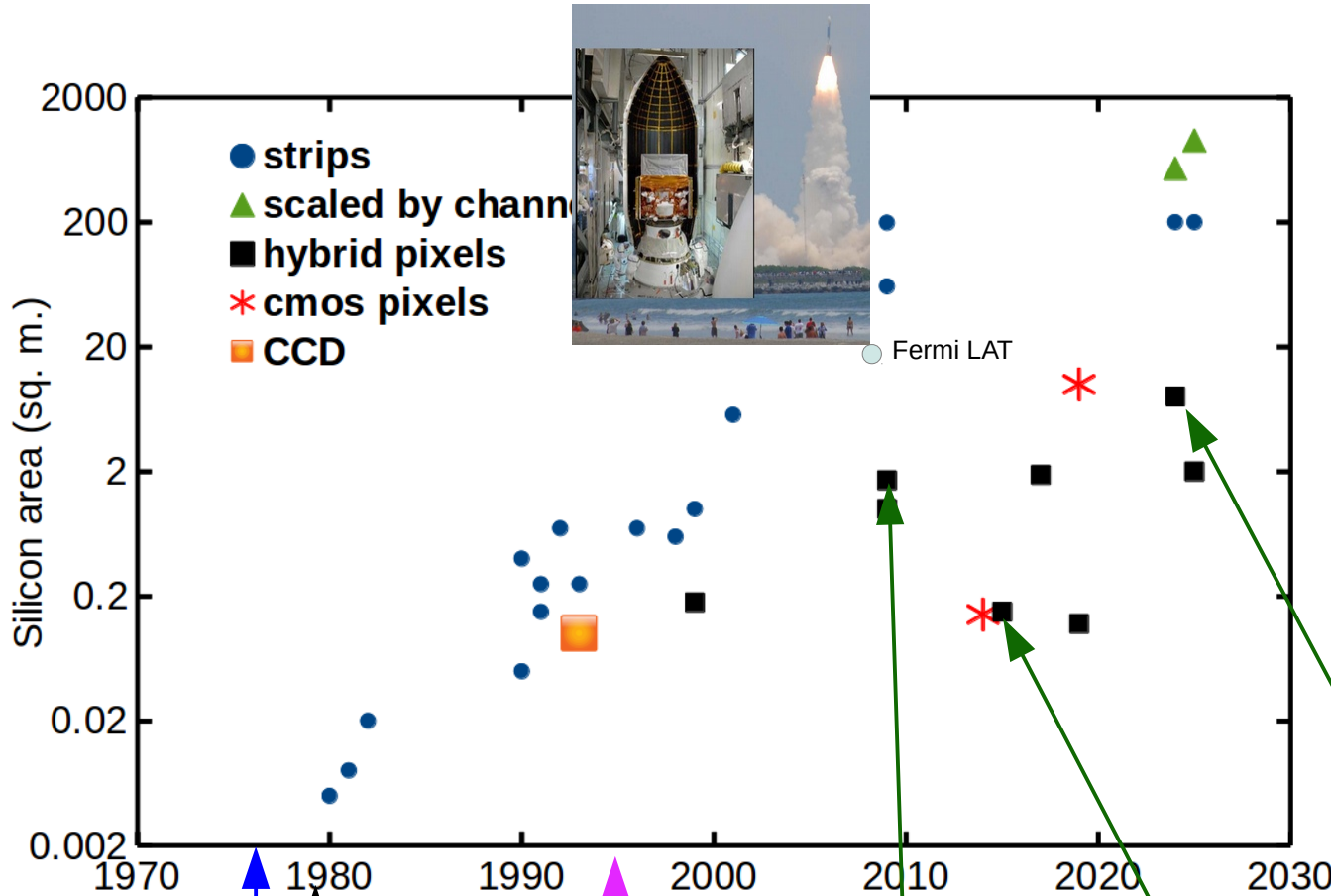
High rate pixel readout chips are memories (in addition to being pixel readout chips)



Plot is for a memory module containing 8 silicon chips so $B = b$

Figure 2. DDR4 higher performance compared with DDR3L and DDR2

(and this is not rad hard)



Strip Detectors

- 1980 NA1
- 1981 NA11
- 1982 NA14
- 1990 MarkII
- 1990 DELPHI
- 1991 ALEPH
- 1991 OPAL
- 1992 CDF SVX
- 1993 L3
- 1996 CDF SVX'
- 1998 CLEO III
- 1999 BaBar
- 2001 CDF SVXII+ISL
- 2009 ATLAS SCT
- 2009 CMS tracker
- 2025 ATLAS ITK
- 2025 CMS upgrade

Hybrid Pixels

- 1999 Delphi
- 2009 ATLAS
- 2009 CMS
- 2015 ATLAS IBL
- 2017 CMS
- 2019 velopix
- 2025 ATLAS
- 2025 CMS

CMOS Pixels

- 2014 STAR
- 2019 ALICE

CCDs

- 1993 VXD

First CCD digital cameras

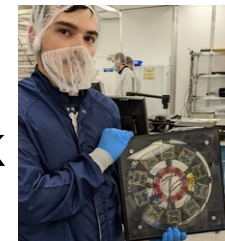
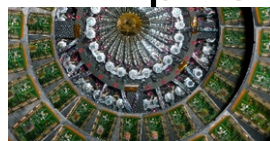
Start of HEP IC design

Year of first data taking
CMOS sensors used in webcams

pixel

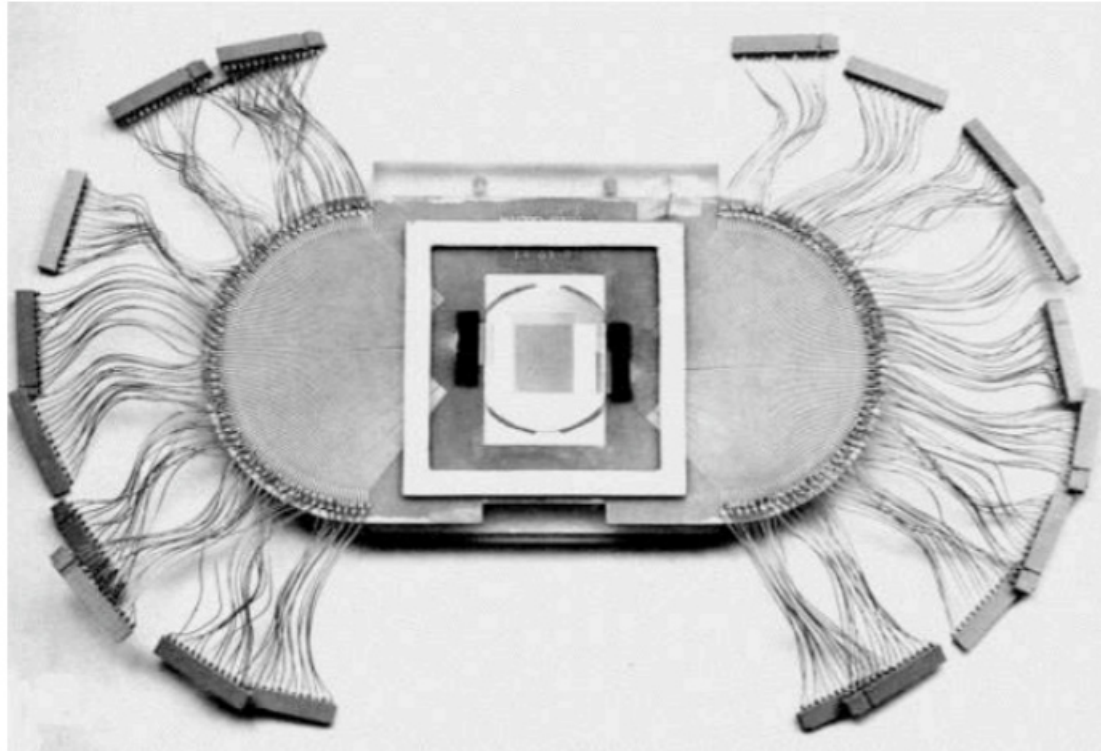
IBL

ITk



Because this was a silicon strip module before:

NA11, CERN 1981



NIM205 (1983) 99

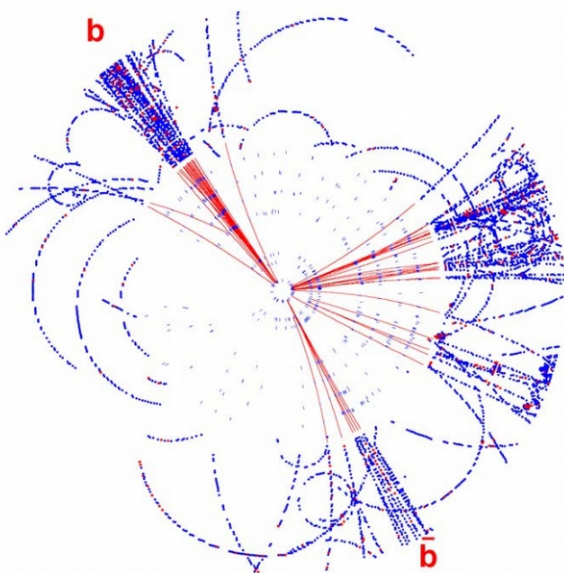
It did not scale

Original ATLAS motivation for pixels circa 1995

ATLAS Barrel Inner Detector

$H \rightarrow b\bar{b}$

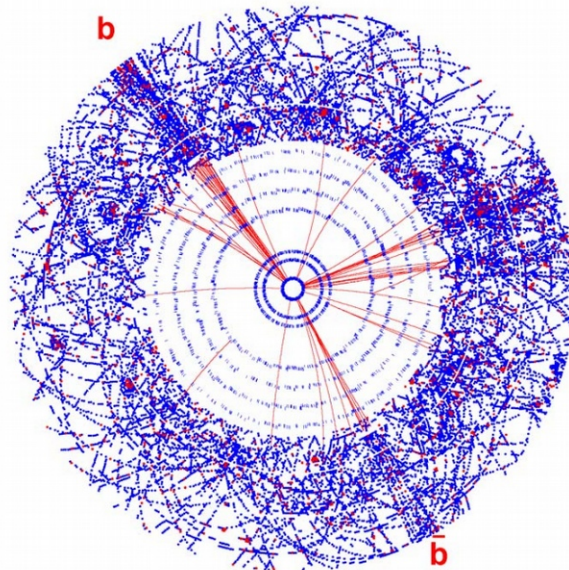
Zero pileup



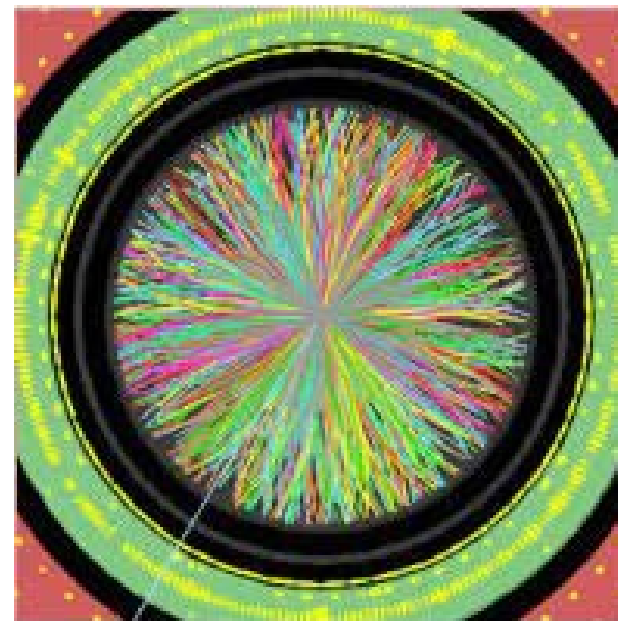
ATLAS Barrel Inner Detector

$H \rightarrow b\bar{b}$

Original design luminosity



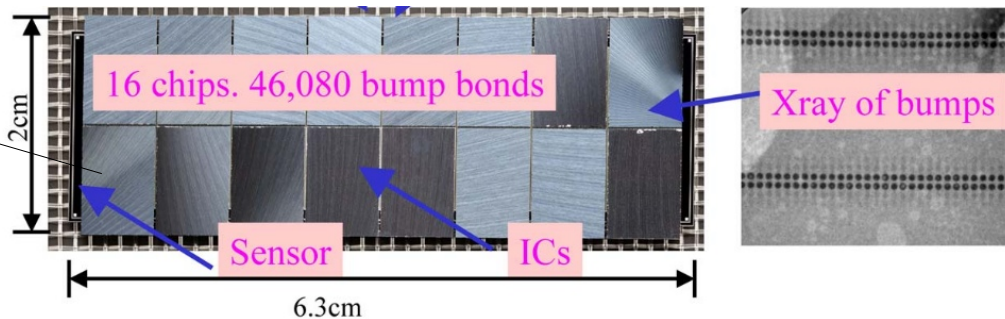
HL-LHC is far beyond



FE-I3 readout chip



Solution:



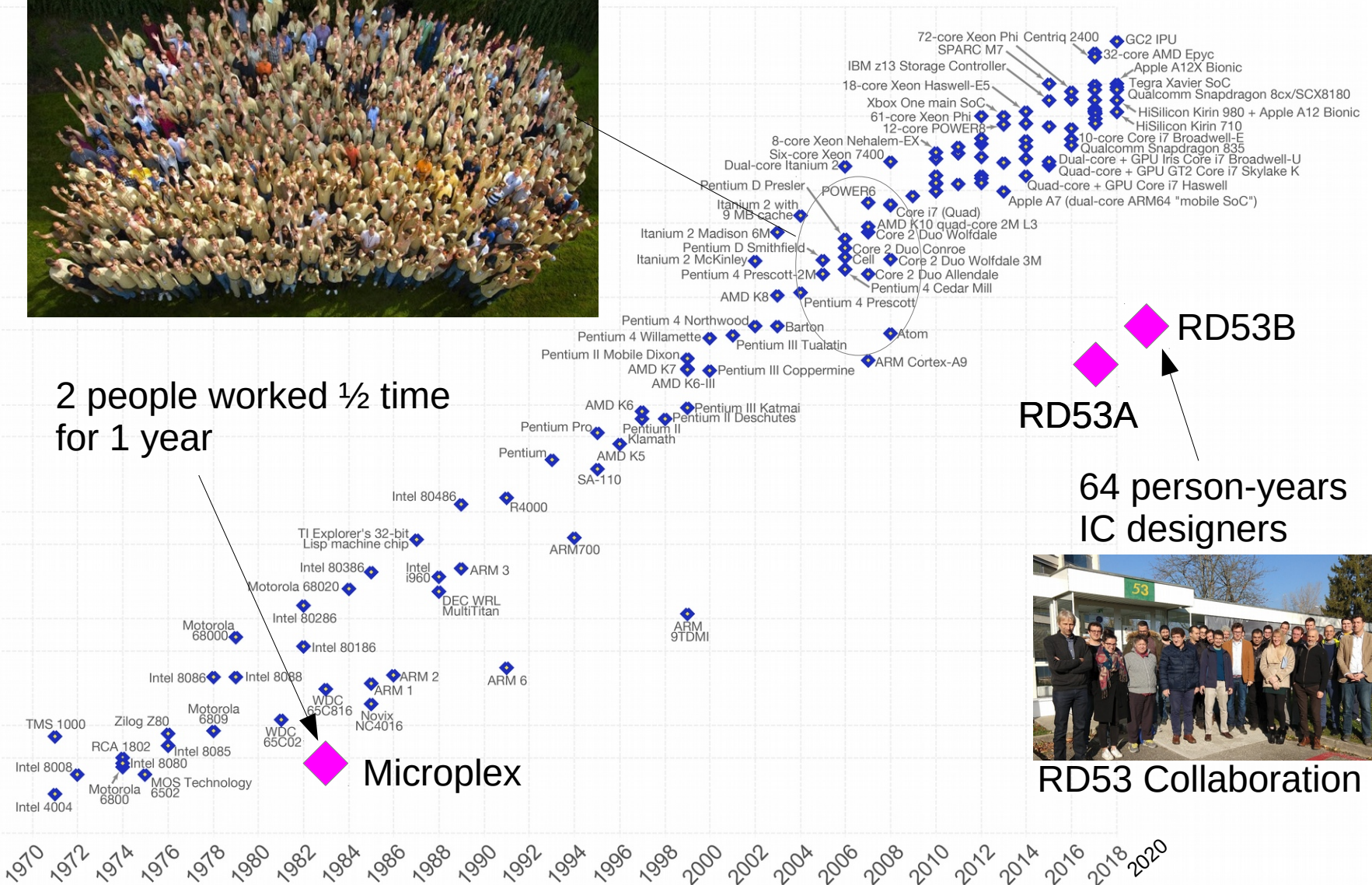
It did not scale.
A new readout chip solution had to be developed

Typical INTEL design team



50,000,000,000
10,000,000,000
5,000,000,000
1,000,000,000
500,000,000
100,000,000
50,000,000
10,000,000
5,000,000
1,000,000
500,000
100,000
50,000
10,000
5,000
1,000

2 people worked 1/2 time for 1 year



RD53A
RD53B
64 person-years IC designers



RD53 Collaboration

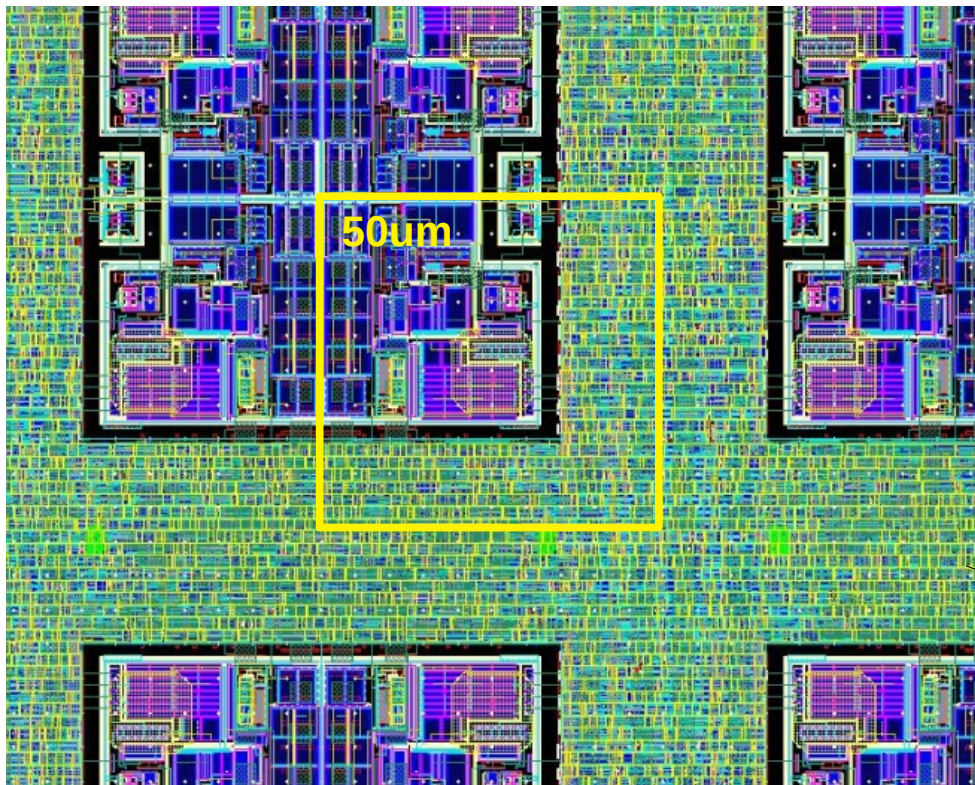
Cern.ch/rd53



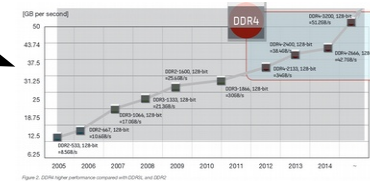
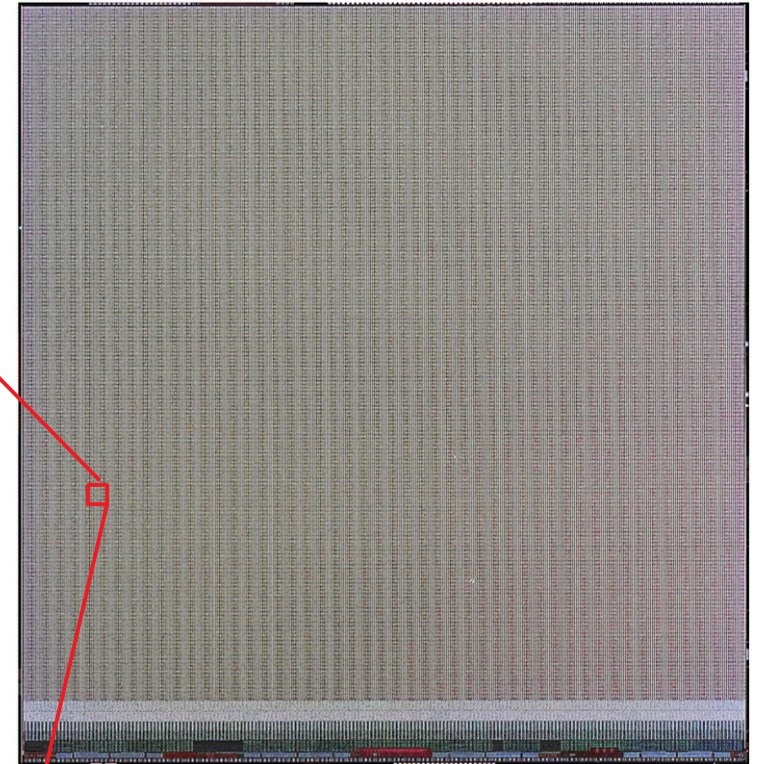
RD-53 Collaboration Home

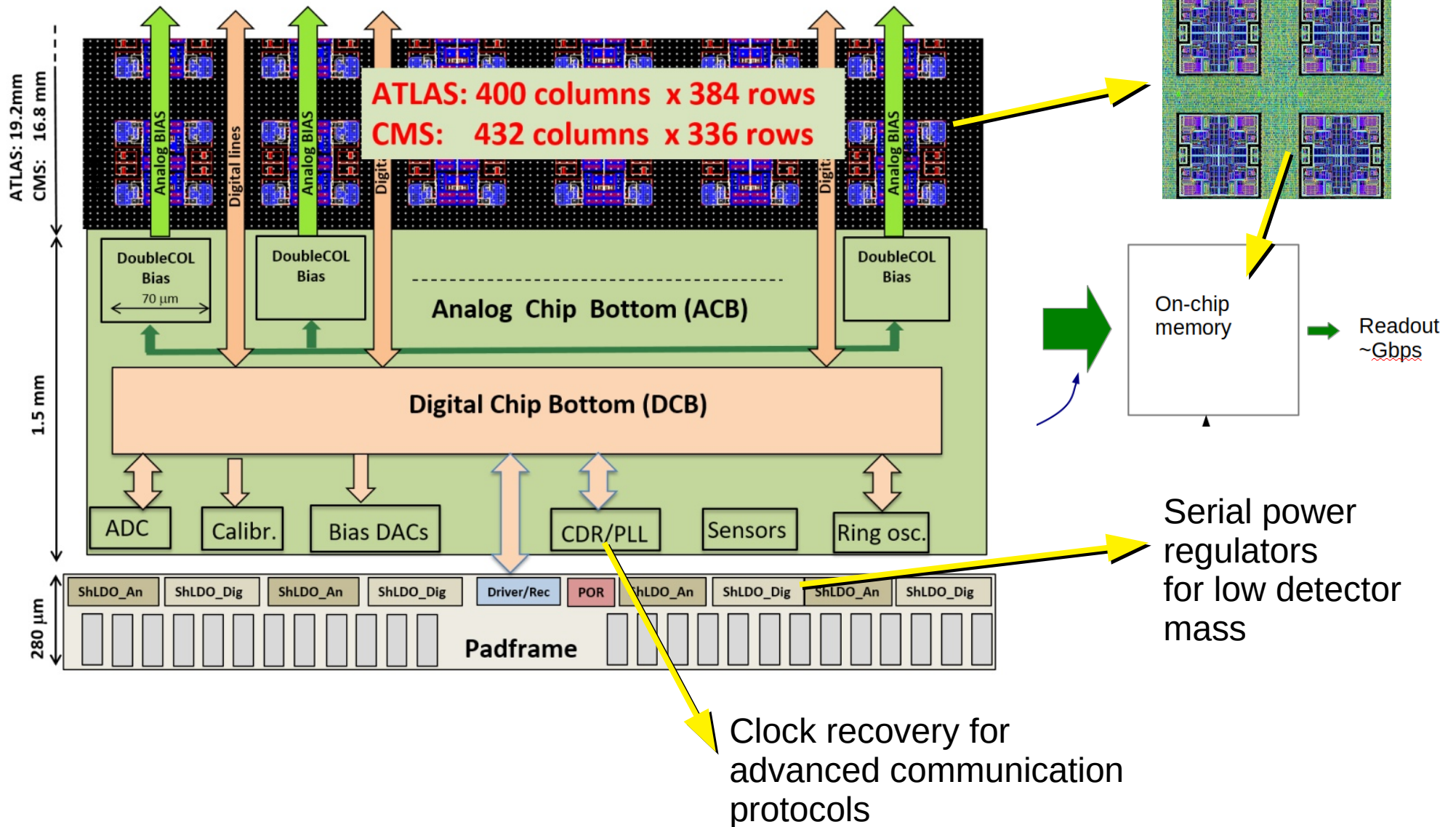


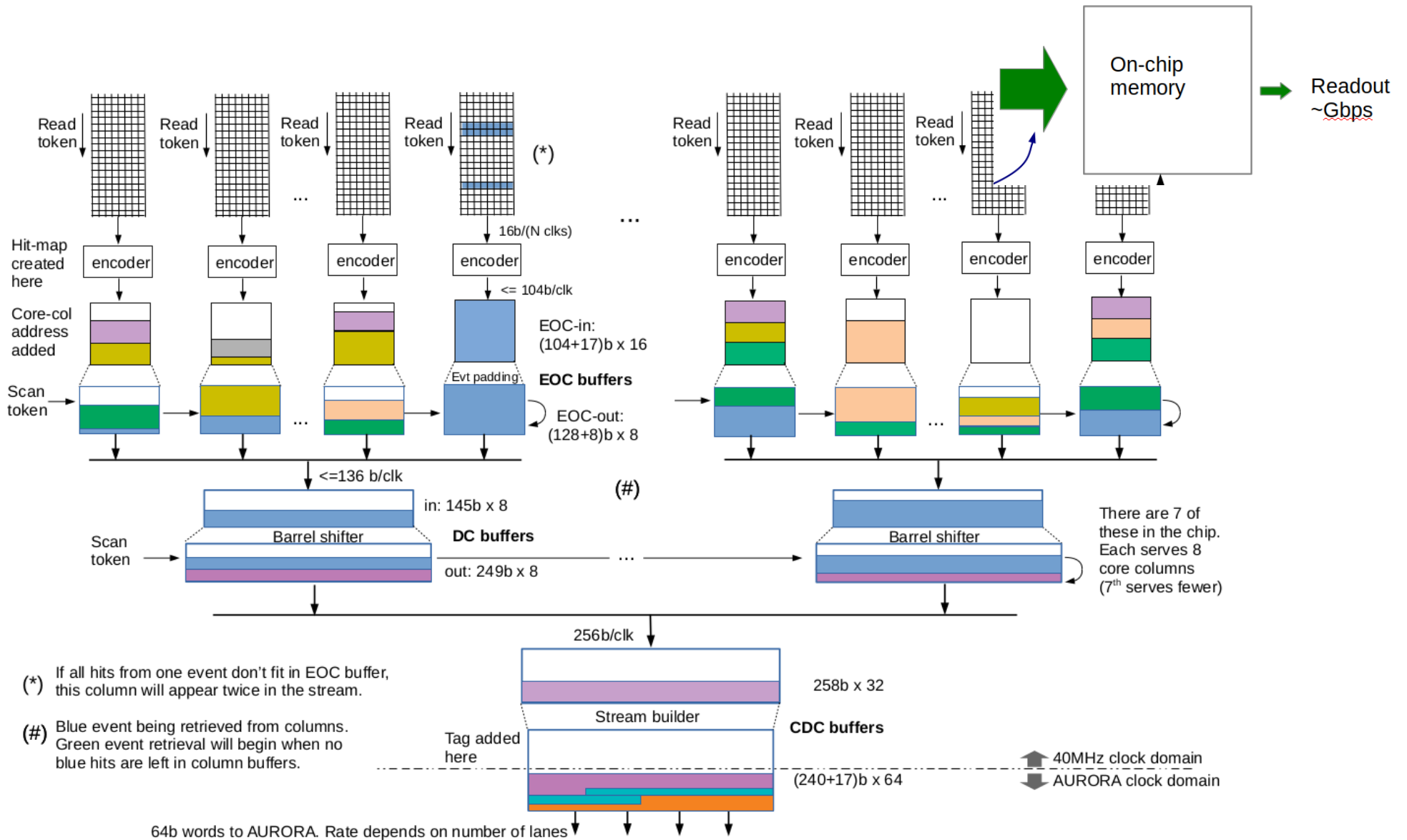
RD-53 will design and produce the next generation of readout chips for the [ATLAS](#) and [CMS](#) pixel detector upgrades at the [HL-LHC](#). More details can be found in the [2018 extension proposal](#) and the original [collaboration proposal](#).

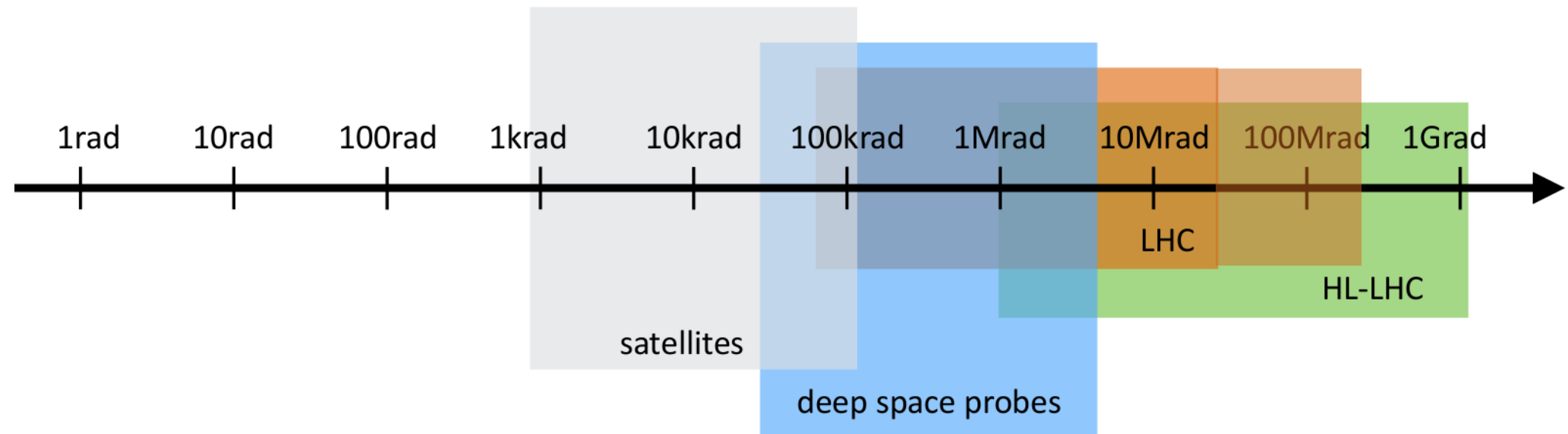


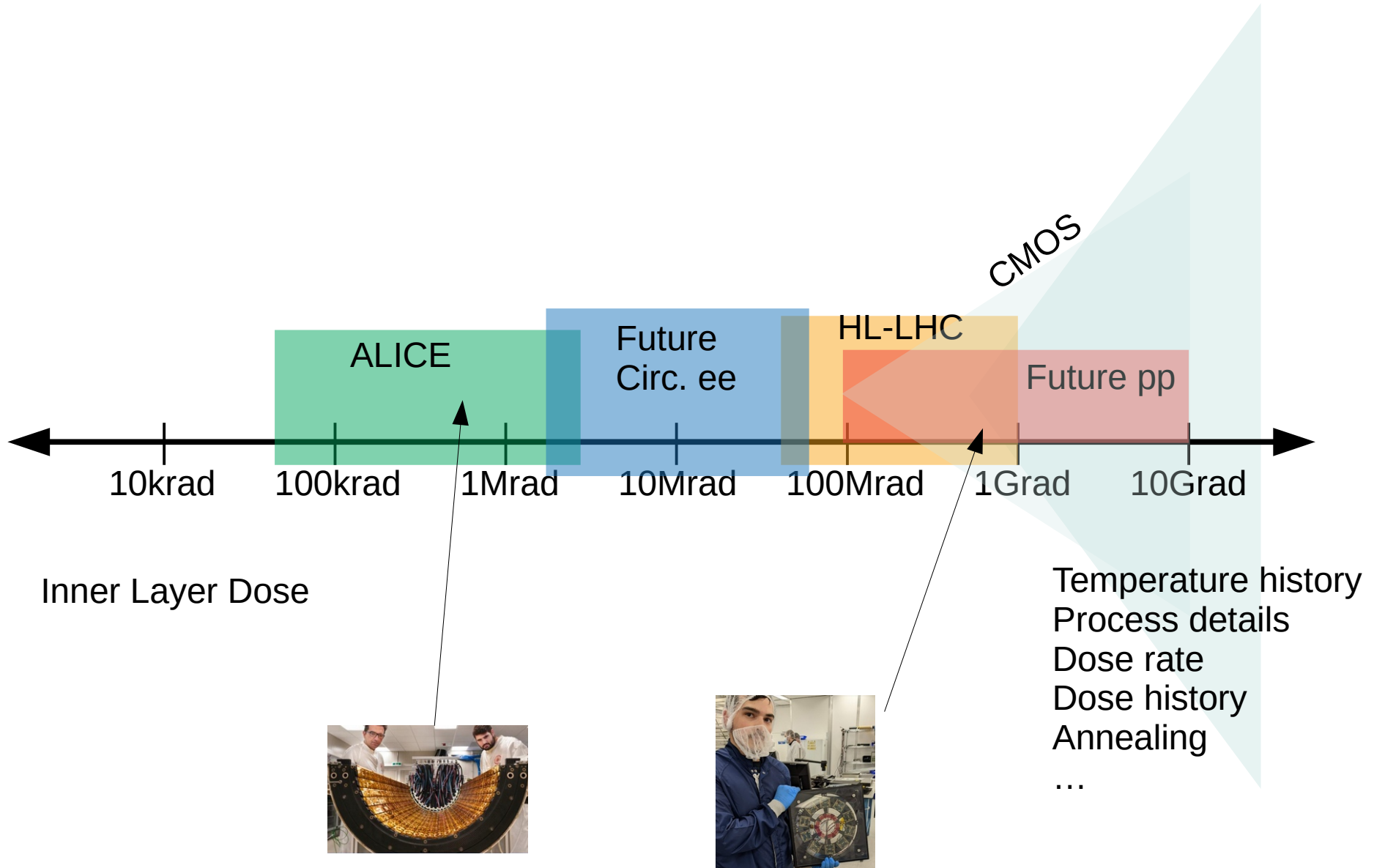
~1000 transistors

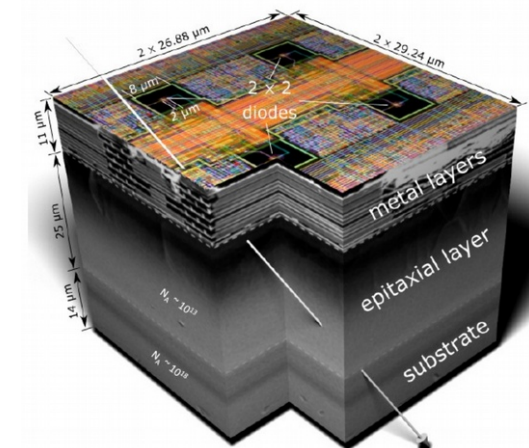
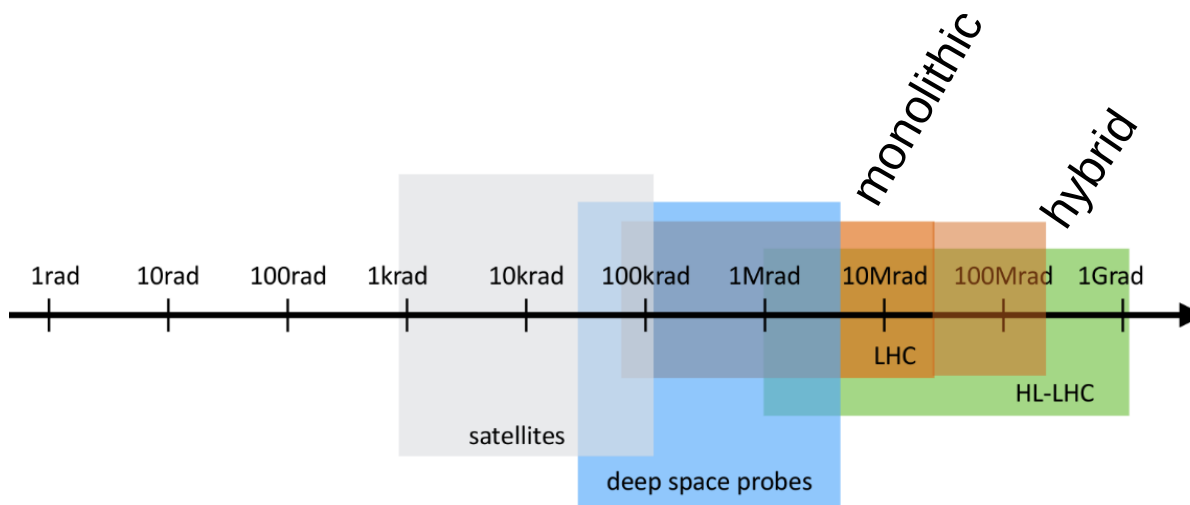
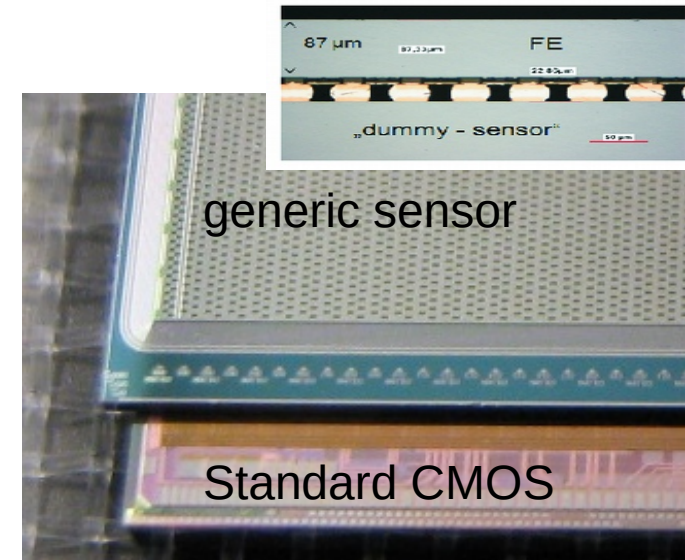
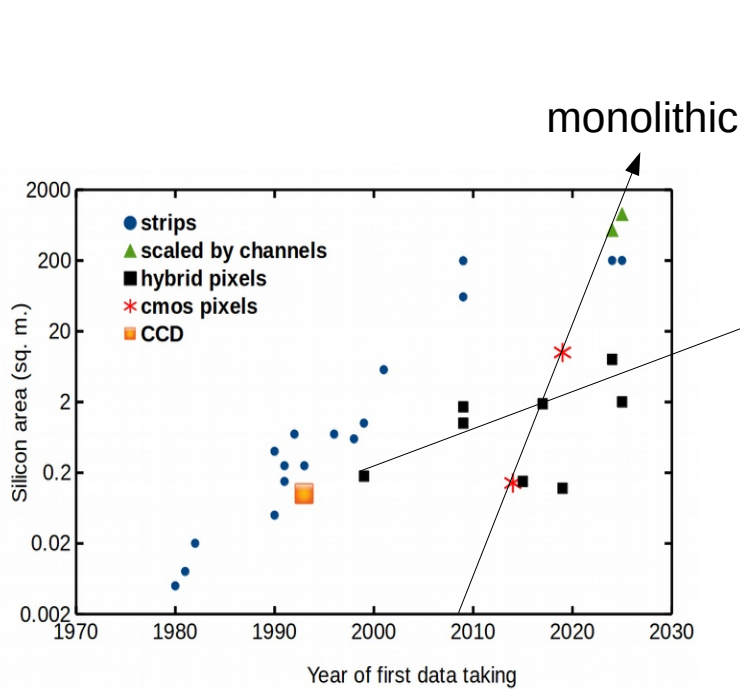




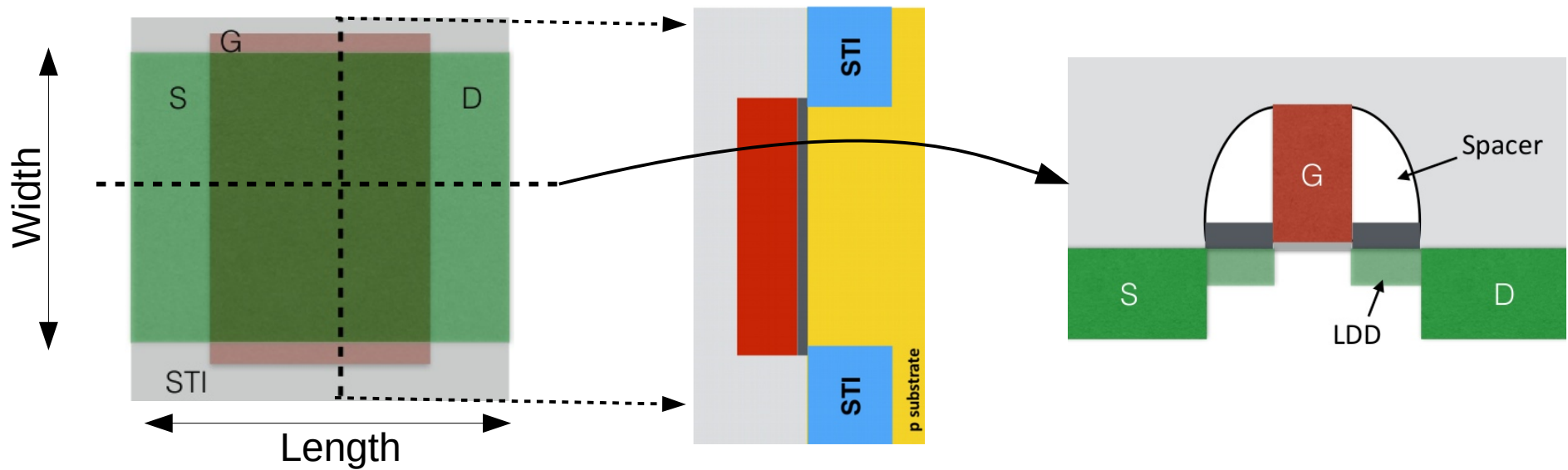
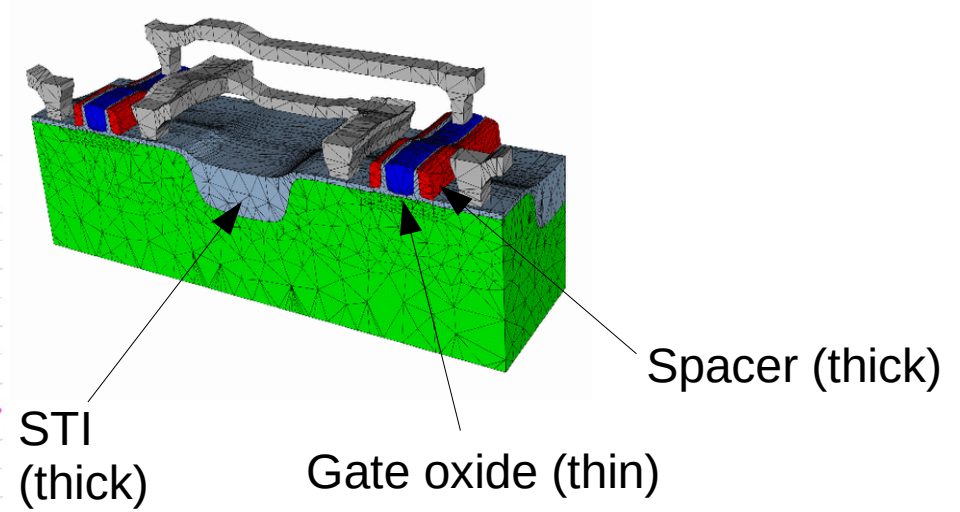
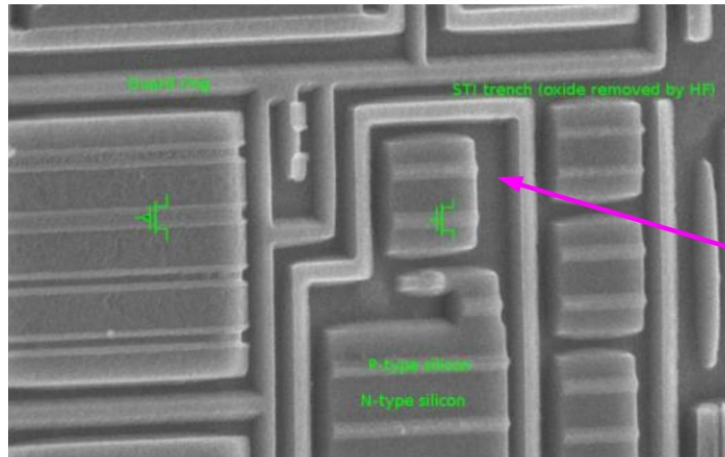








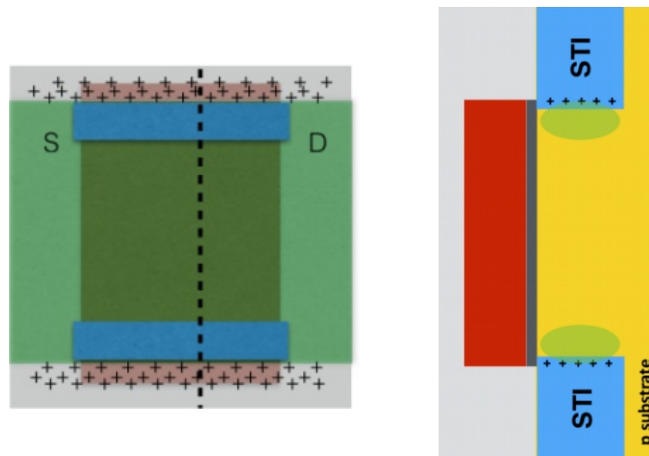
- Change in effective doping is insignificant, because doping levels in CMOS transistors are very high.
- All radiation damage effects to CMOS are due to parasitic electric fields from charge trapped in oxides and oxide-silicon interfaces
- Meet the oxides:
 - Gate oxide
 - Field Oxide
 - Buried Oxide (only for SOI)
 - Shallow trench Isolation (STI)
 - Gate Spacer



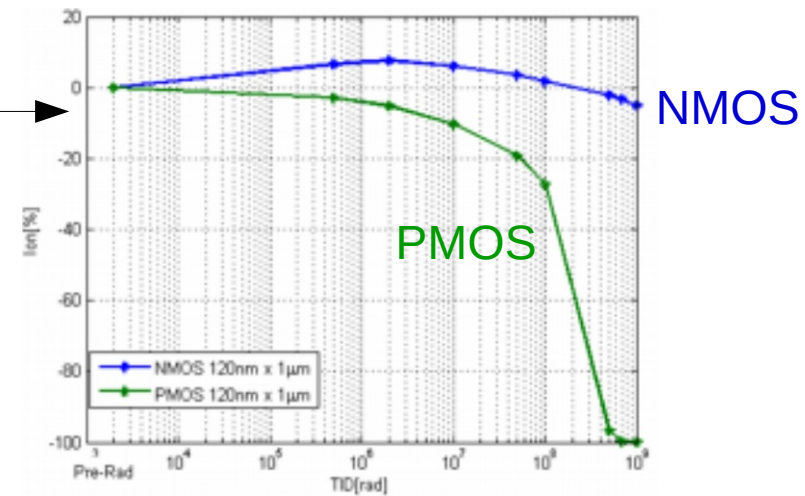
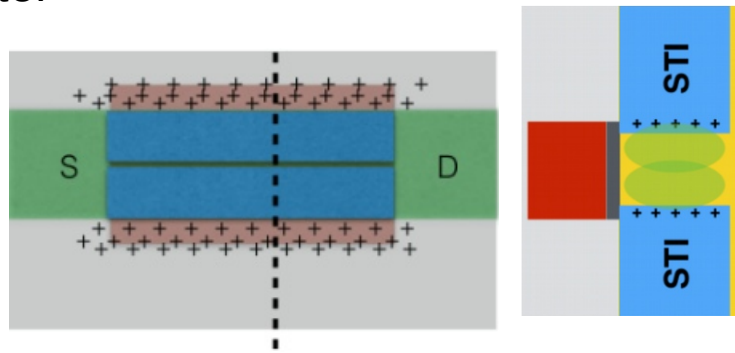
Radiation Induced Narrow Channel Effect

F. Faccio and G. Cervelli, "Radiation induced edge effects in deep submicron CMOS transistors",
 IEEE Trans. Nucl. Science, Vol.52, N.6 (2005) pp.2413-2420 <http://dx.doi.org/10.1109/TNS.2005.860698>

Wide Transistor



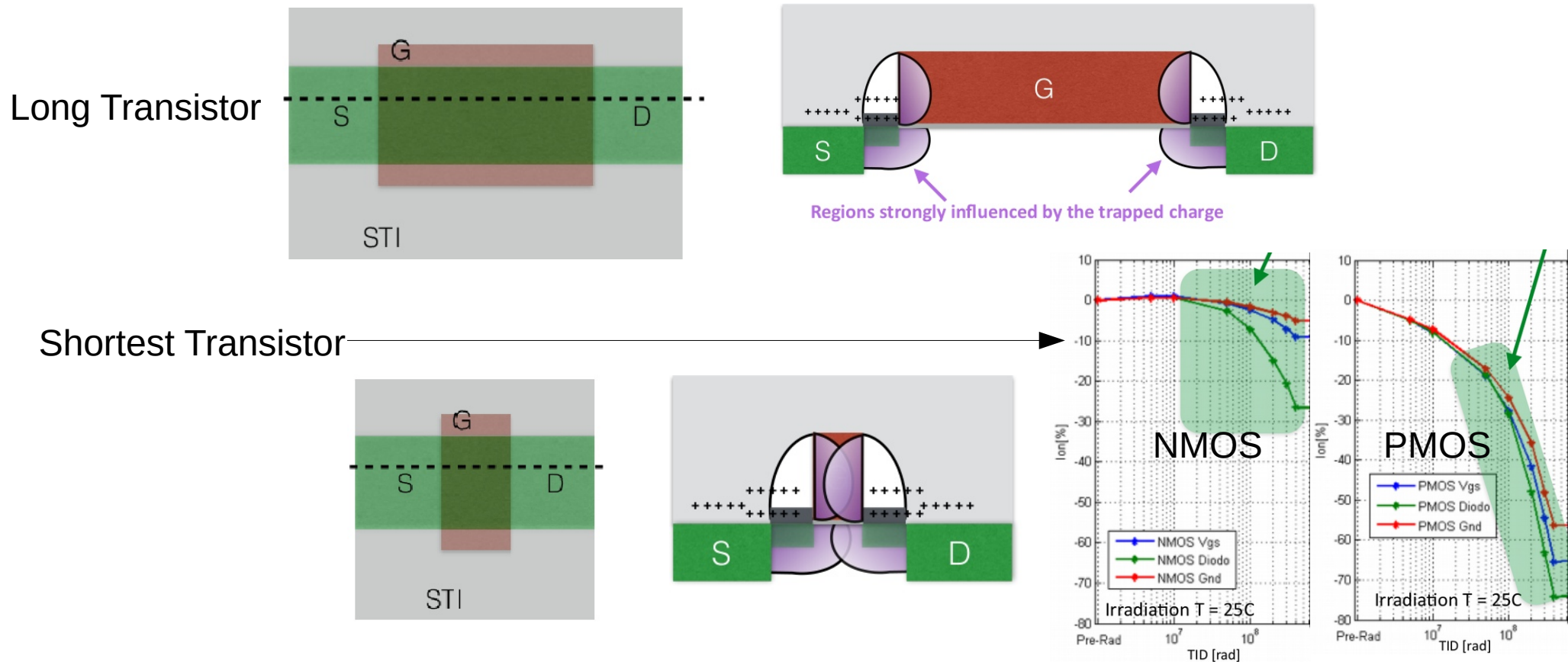
Narrowest Transistor



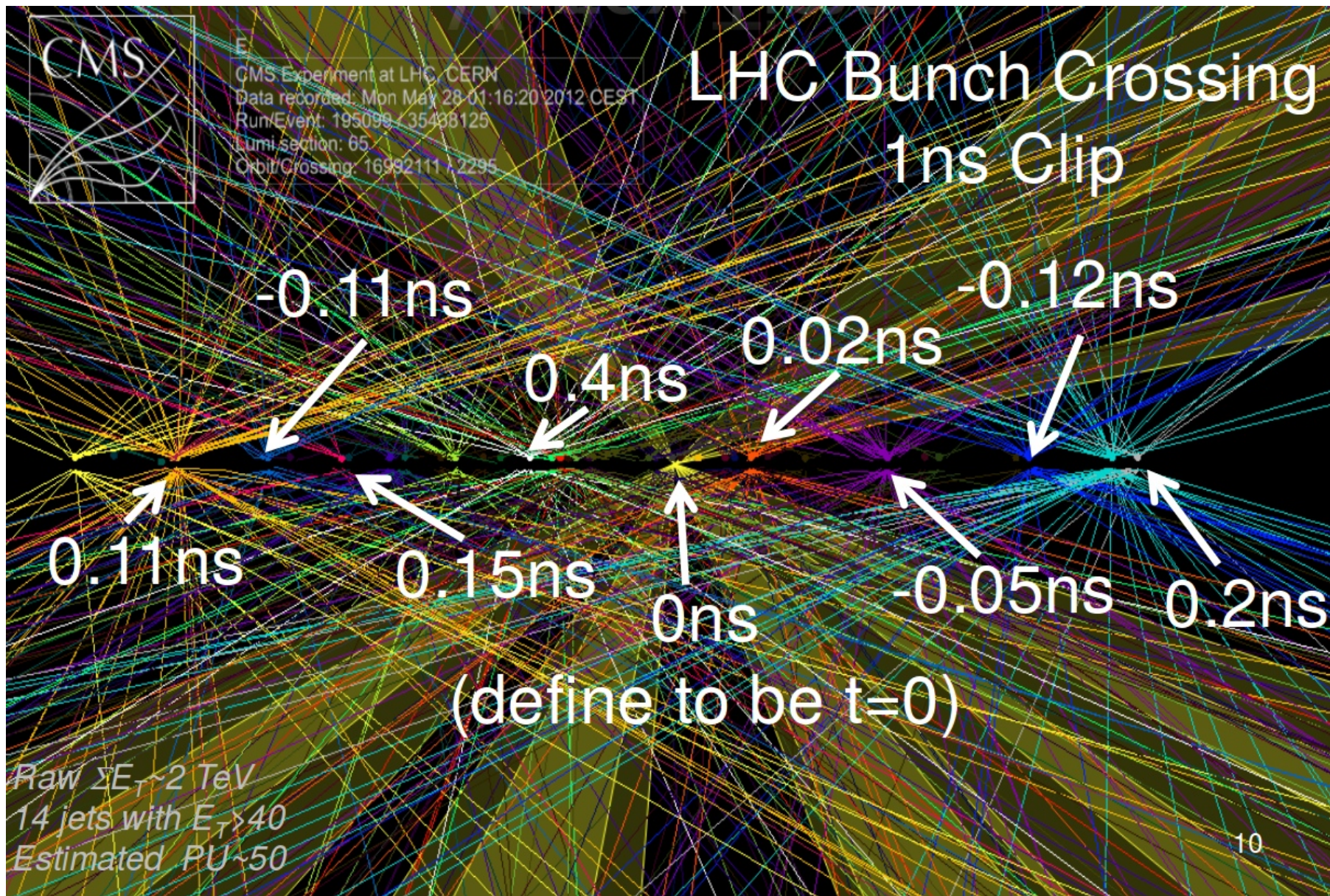
1Grad

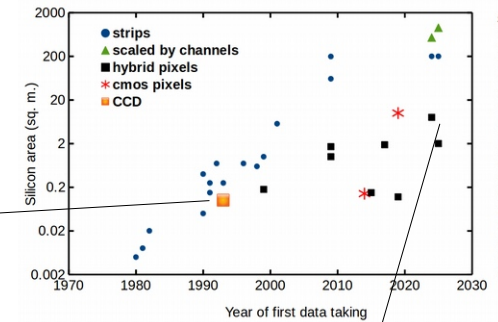
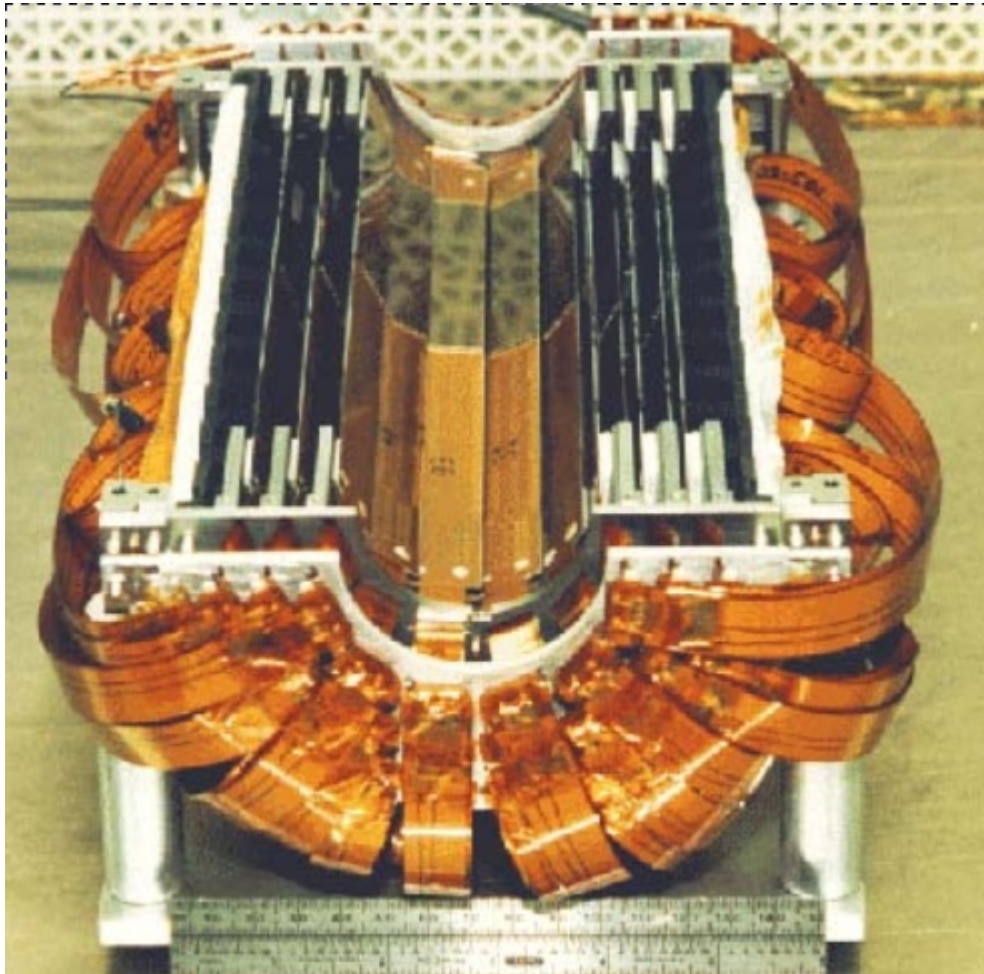
Radiation Induced Short Channel Effect

F. Faccio et al., "Radiation-Induced Short Channel (RISCE) and Narrow Channel (RINCE) Effects in 65 and 130 nm MOSFETs,"
 IEEE Trans. Nucl. Science, Vol.62 , N.6 (2015) <http://dx.doi.org/10.1109/TNS.2015.2492778>



- Imaging particles is an inverse problem to typical imaging
- Need to surround the source of particles with sensors – large area of silicon needed
- Plus frame rate is in the MHz
- => Custom ICs needed
- CMOS sensors for particle detection scale better to large areas, but have limited rate and radiation hardness and need highly customized fabrication process.
- Hybrid detectors can use standard CMOS for readout (custom design but not custom process) and radiation optimized sensors.
- Design of radiation hard ASICs is a cottage industry in HEP



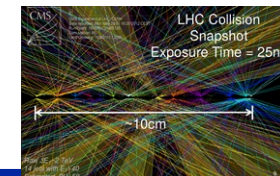


SLD VXD

- Silicon area: 0.12 m²
- 300M pixels (20μm x 20μm)
- But only 350,000 Z decays recorded
- => most pixels were never hit by real collision particle!

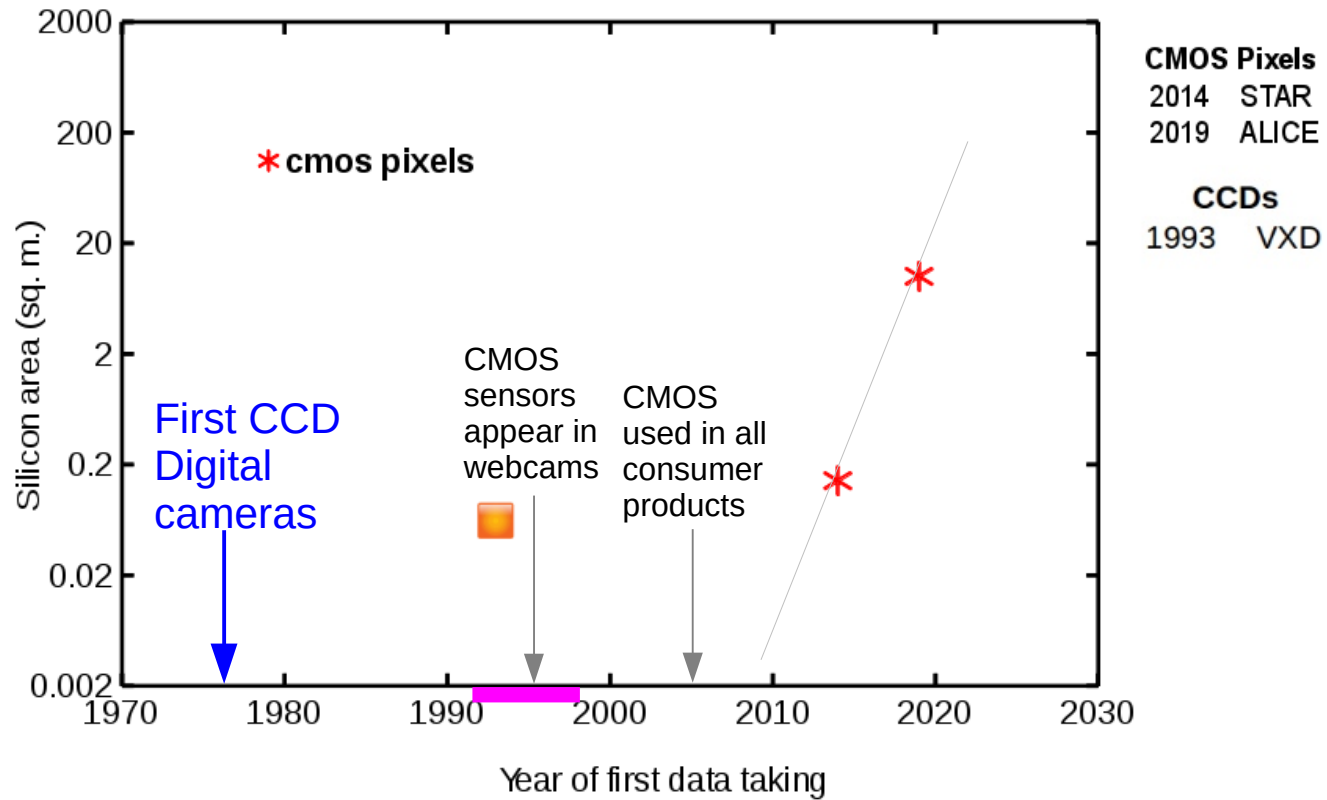
HL-LHC

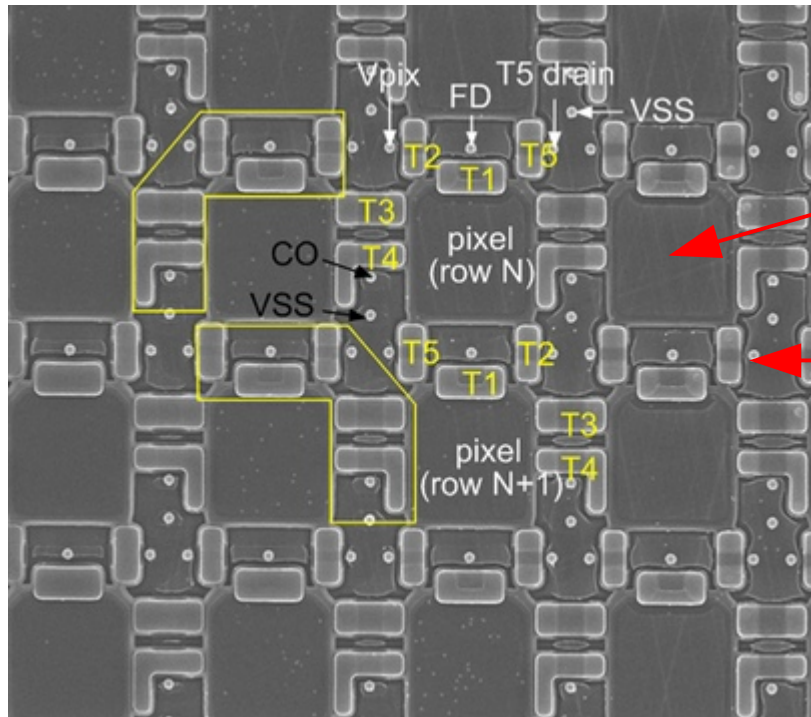
- Inner layers of ATLAS and CMS high luminosity upgrades will see 10 collision particles in every Si atom!



X 10¹⁶

BACKUP





Photodiode covers about half the pixel area in this example

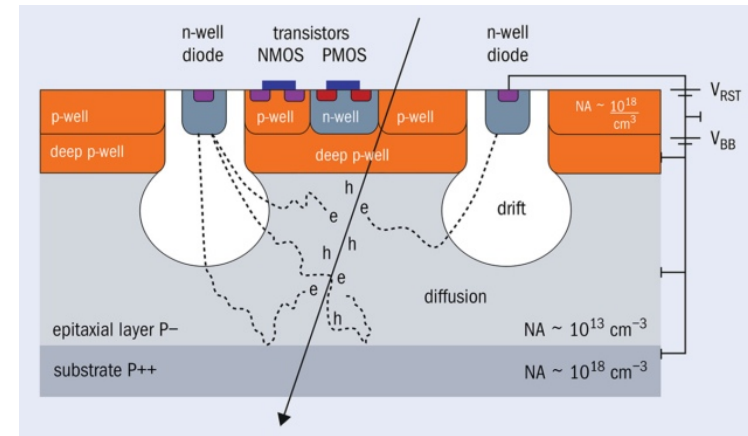
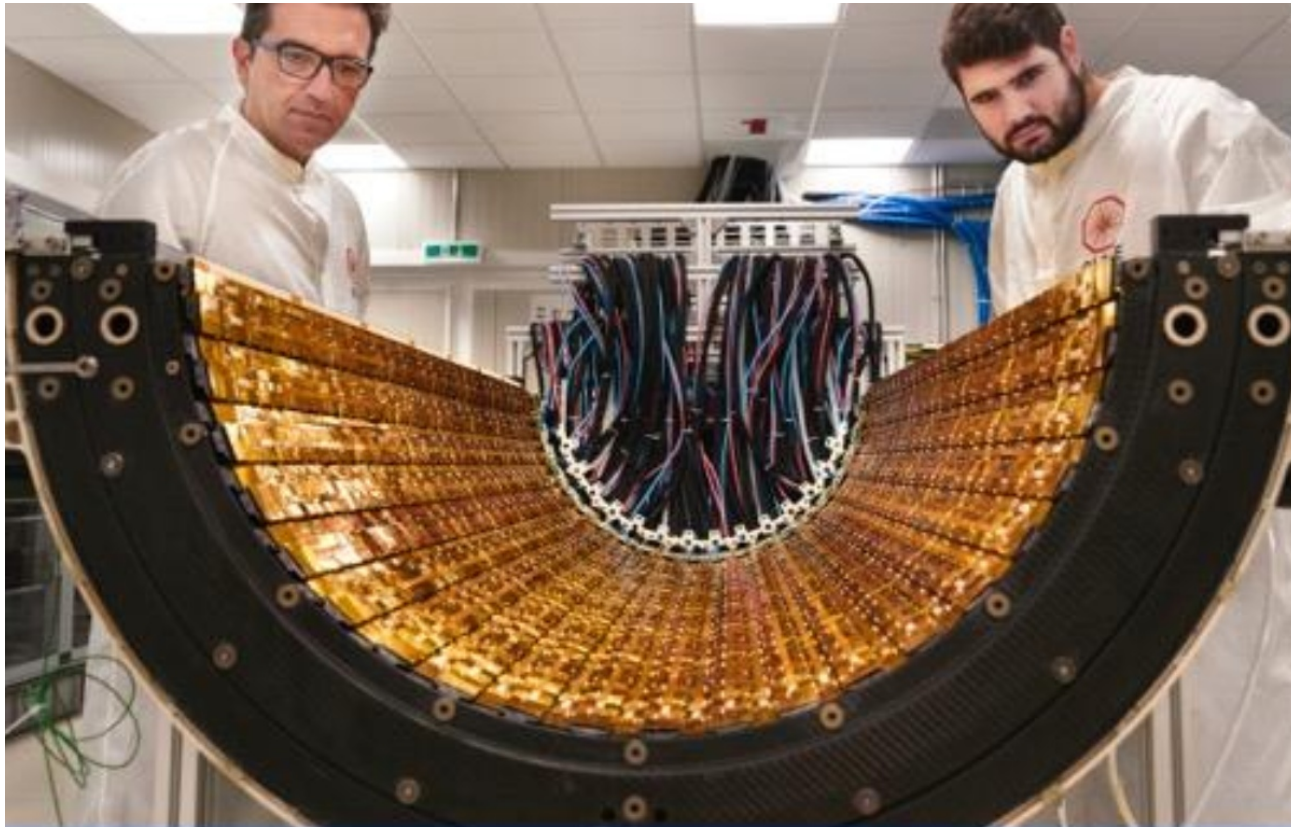
Metal traces have been removed. They run over the transistors leaving photodiode exposed

For particle tracking need 100% fill factor

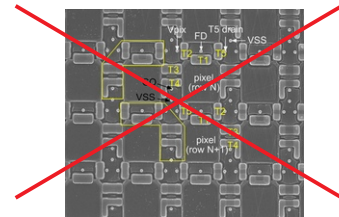
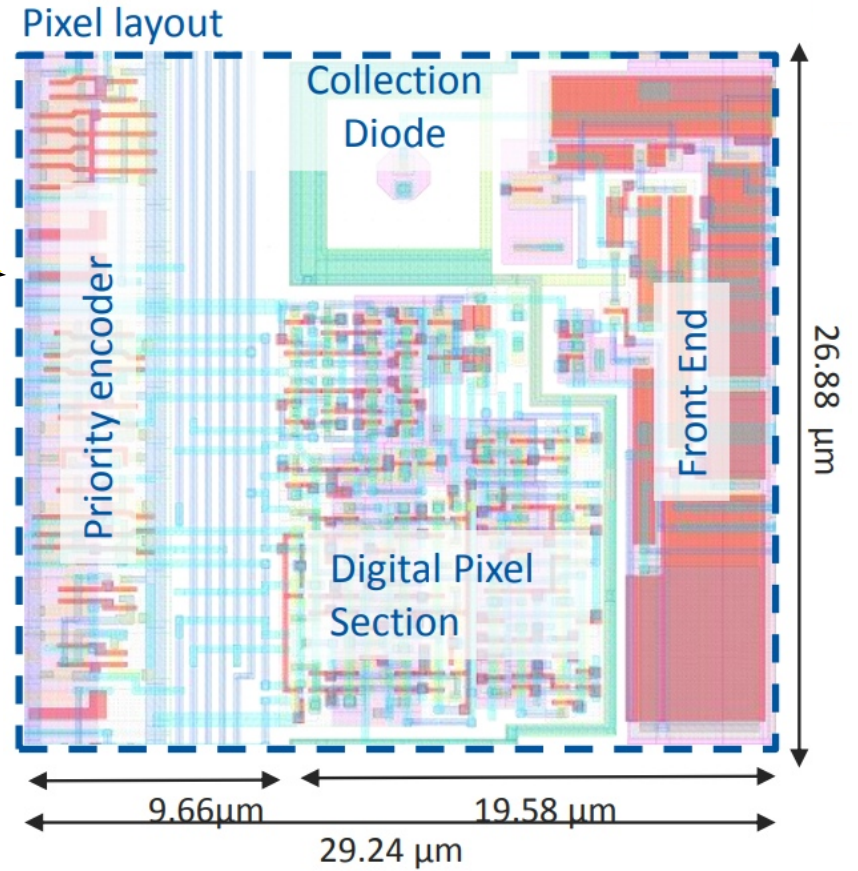
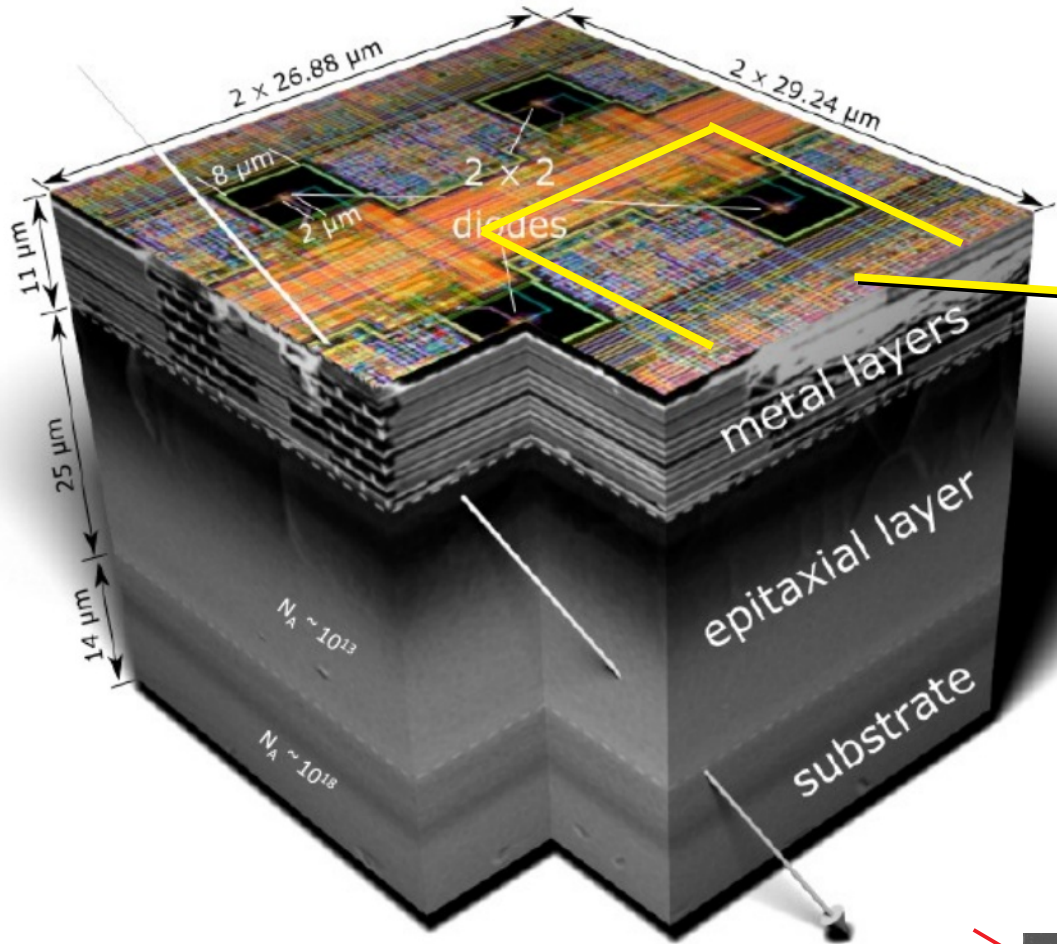
Need low enough noise that can detect a single particle

Need radiation hardness

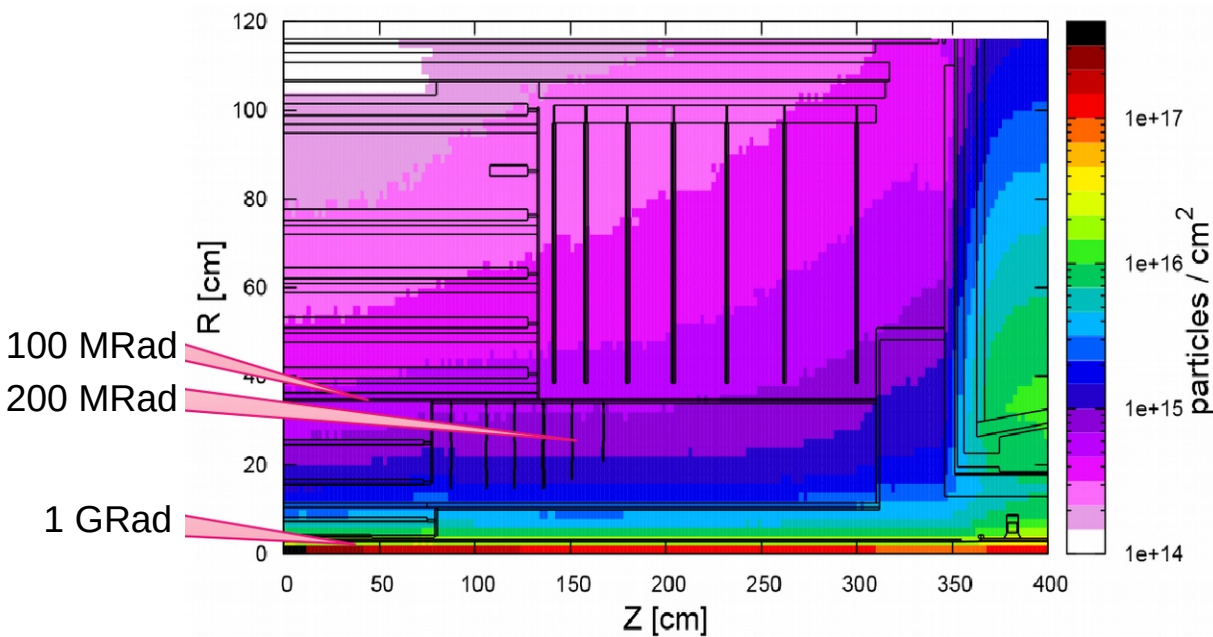
ALICE just installed a 10m² tracker made of CMOS sensors



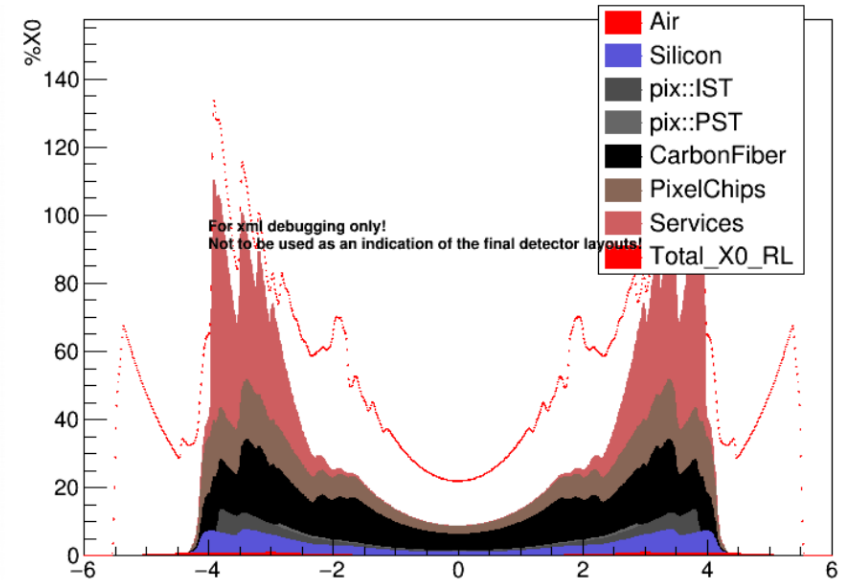
Highly customized CMOS process. Proprietary. Not portable



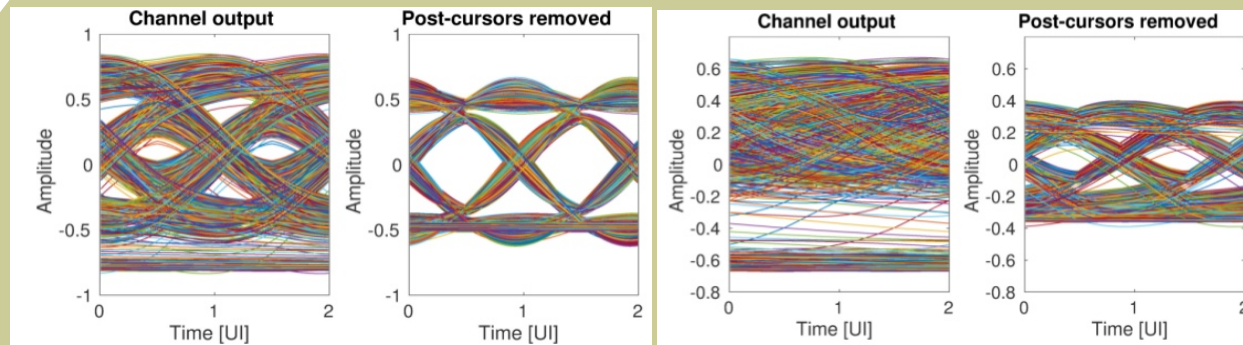
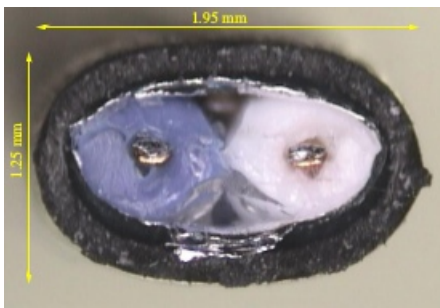
~100 transistors



Can't use optical transmitters



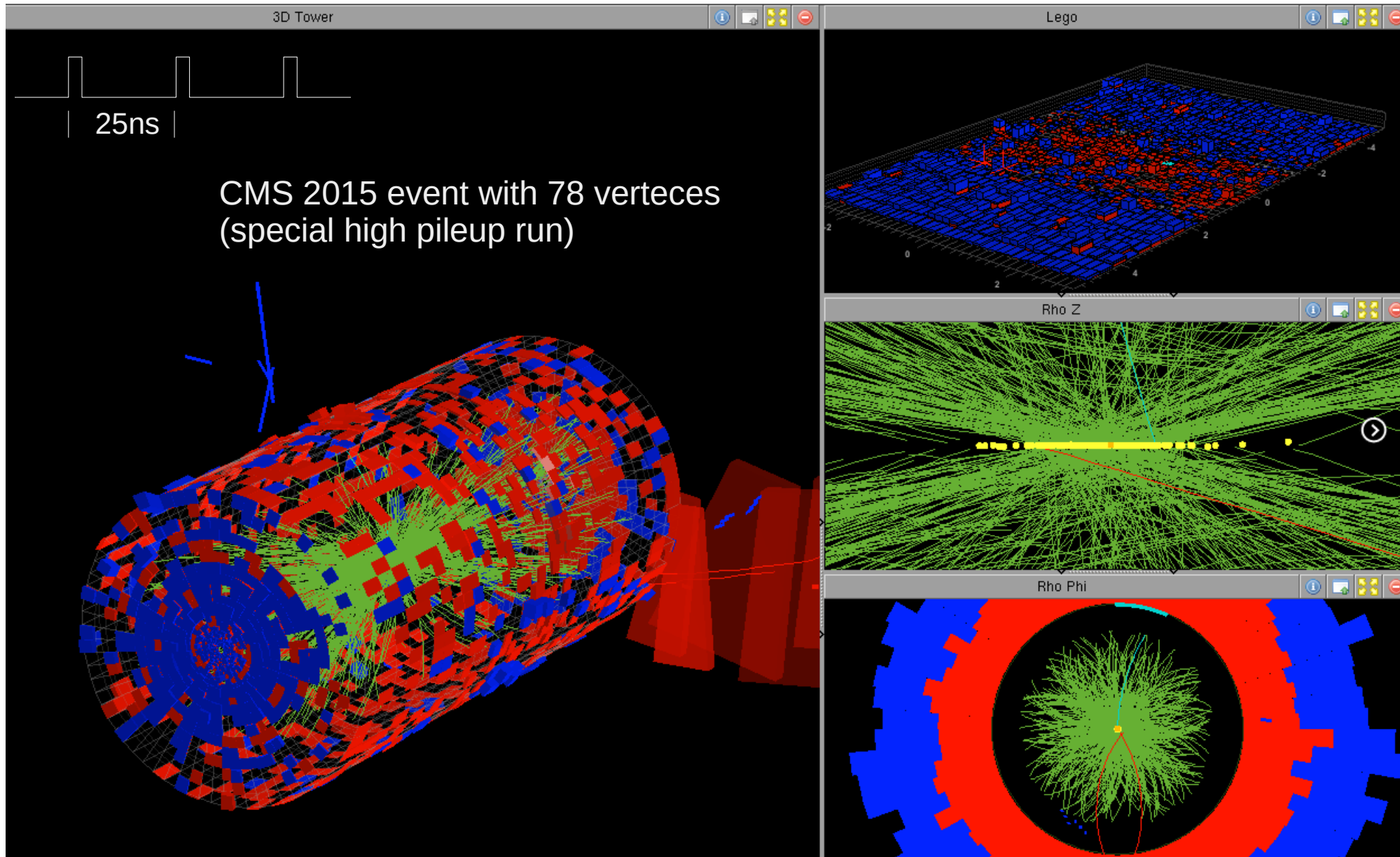
Can't use heavy shielded cables

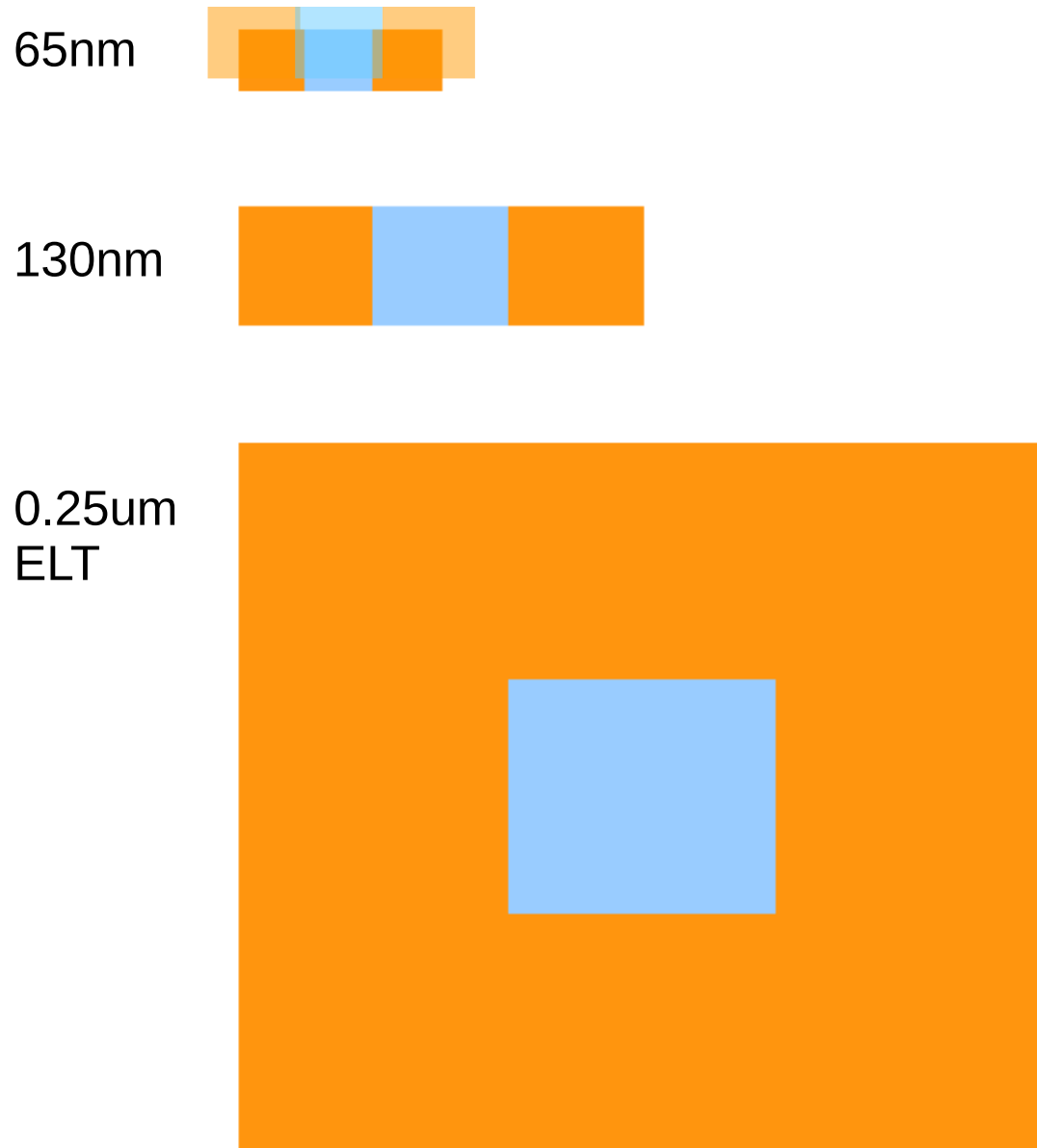


3m

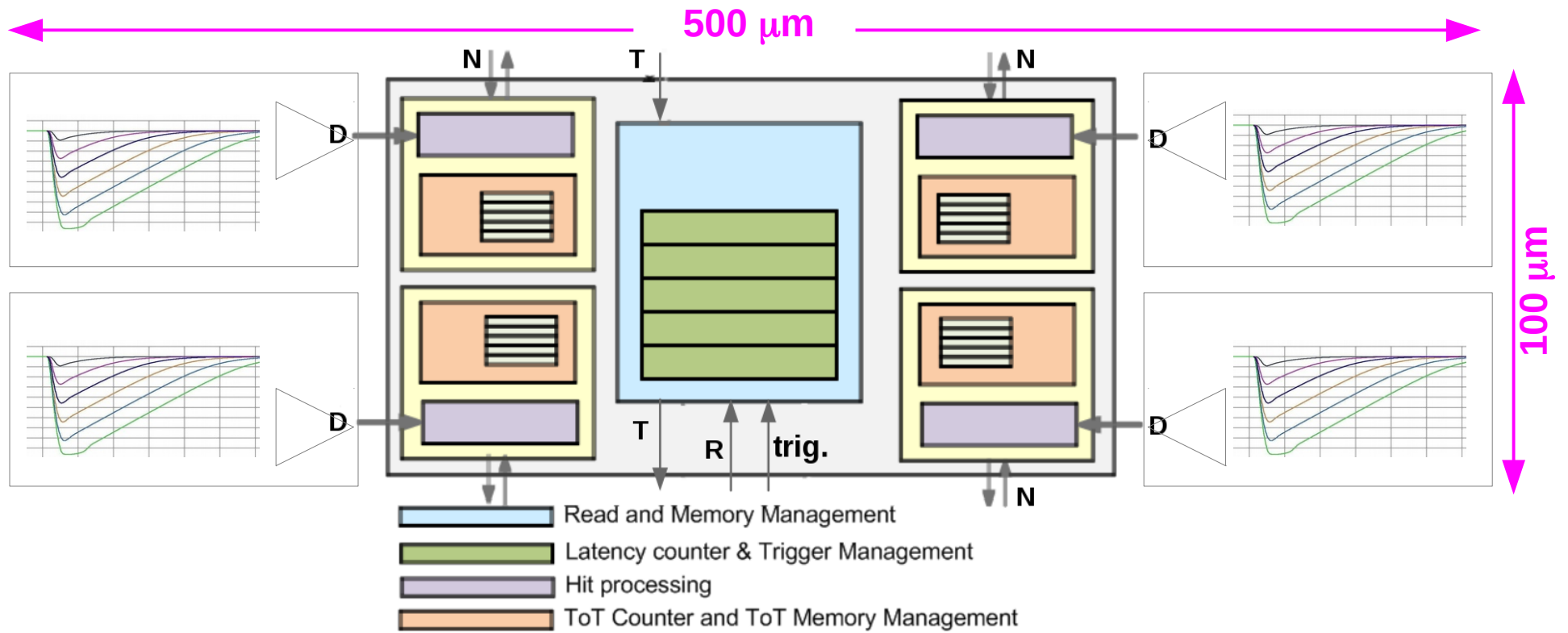
5Gbps Simulation

5m

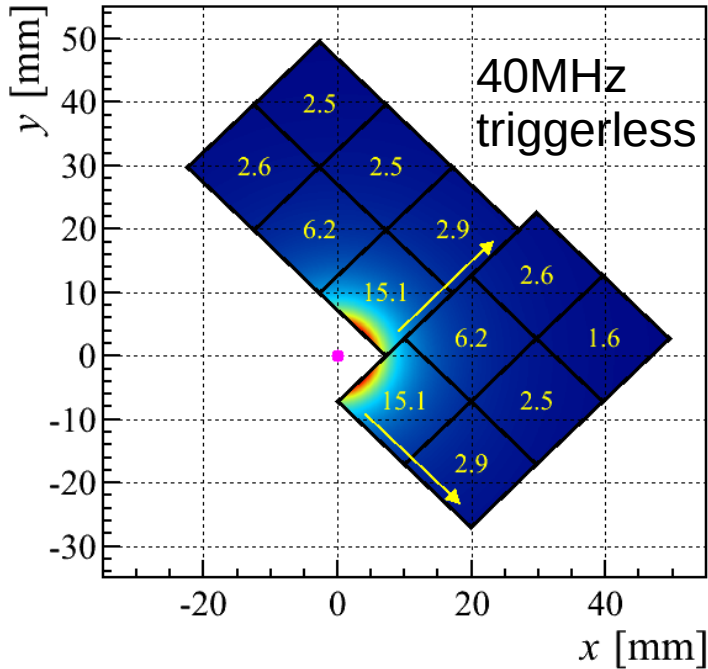




- Digital block is shared with 4 inputs- each form an identical analog pixel.



Readout chips in LHCb Velopix plane
Output data rate per chip in Gbps



- Geometry looks like data flow diagram
- Lots of room outside physics acceptance
- Can have many cables out of each chip

Velopix half with 26 planes

